

The Influence of Contamination on the Thermal and Phase Stability of Nanocrystalline Ni-W Alloys

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LEHIGH
UNIVERSITY



Grain Boundary Velocity

Grain Growth
Driving Forces

Must stop
grain growth!

Energetic

Physical

$$v \propto M \gamma \kappa$$

GB Velocity

GB Mobility

Two Strategies

“Thermodynamic”

TABLE I. Thermal stabilization of nanocrystalline materials by the thermodynamic mechanism of solute segregation to grain boundaries.

Material	Solute addition	Maximum T/T_m	Reference
Ni	6, 13 at.% W	0.49, 0.58	24
Co	1.1 at.% P	0.42	30
Fe	1–4 at.% Zr	0.59–0.65	31, 32
Fe–Cr	1–4 at.% Zr	0.65	33
Ni	3.6 at.% P	0.34	29
Y	5–20 at.% F	0.36–0.42	35
RuAl	~15 at.% Fe	0.55	36
TiO ₂	0.34 mol% Ca	<0.55	37

Ni-W and Ni-P Alloys

“Kinetic”

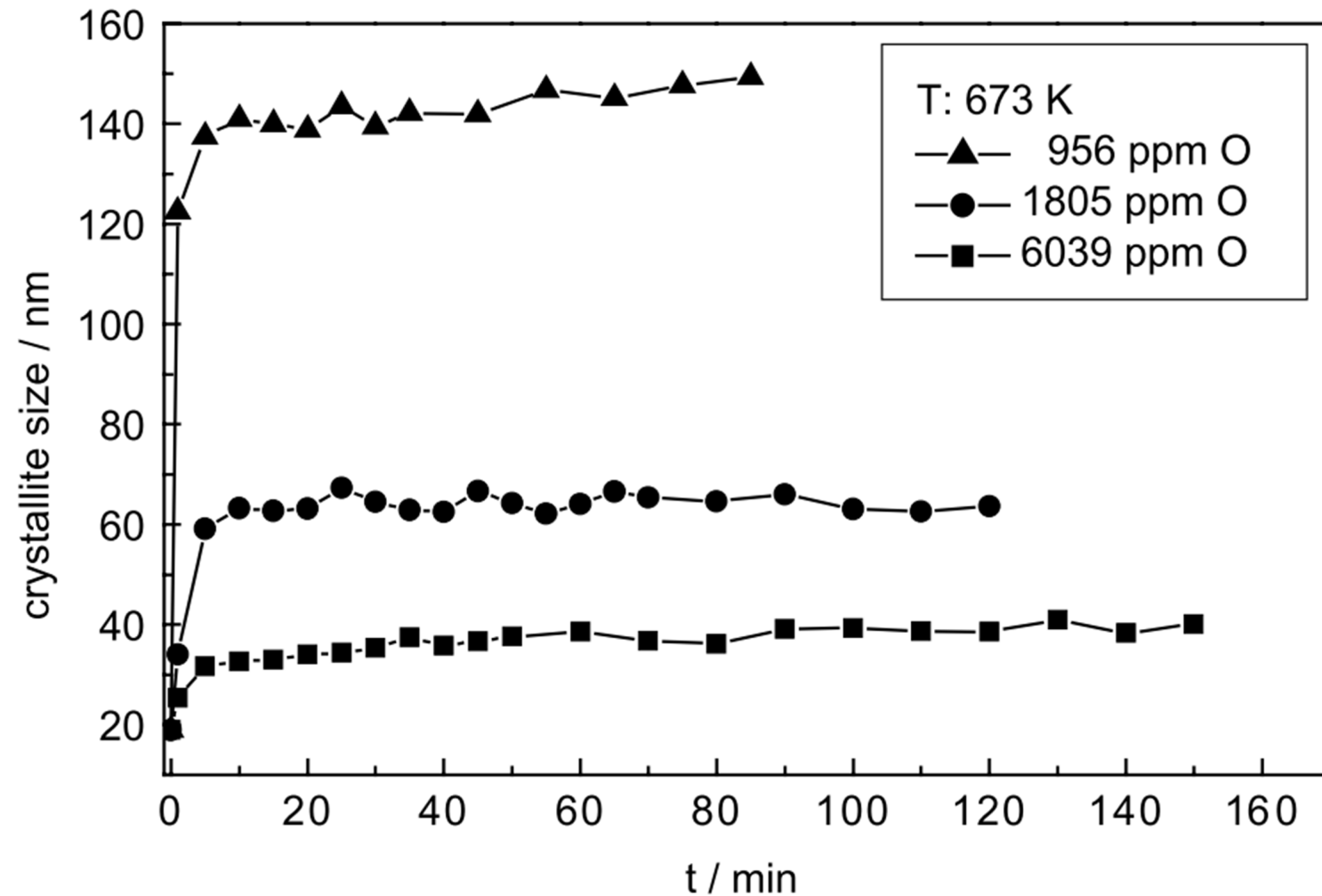
TABLE II. Thermal stabilization of nanocrystalline materials by the kinetic mechanism of Zener Pinning by nanoscale particles.

Material	Particle	Maximum T/T_m	Reference
Al (99.9%)	Al ₂ O ₃ , Al ₄ C ₃ ~5 nm	0.78	43
Fe–10 wt% Al	Al ₂ O ₃ , AlN	>0.68	40
Fe–10 wt% Al	Al ₂ O ₃	0.75	44
Cu–5 at.% Zr	ZrO ₂ , ZrC ~8 nm	0.86	42
Al–7.5 wt% Mg	Al ₂ O ₃ , Al ₄ C ₃	0.78	45
Al ₉₃ Fe ₃ Ti ₂ Cr ₂	Al ₆ Fe, Al ₁₃ Fe ₄ , Al ₃ Ti, Al ₁₃ Cr ₂	0.77	41
Mg–12 wt% Cu	Mg ₂ Cu	0.76	46
Cu–at.% Nb	Nb	0.86	47

Impurity Particles...

Processing Impurities

Oxygen from plating



j_p (mA/cm ²)	t_{on} (ms)	t_{off} (ms)
50	–	–
5	–	–
1	–	–
250	2	8
100	5	95
5	2	8

H (ppm)	C (ppm)	O (ppm)	S (ppm)	Cl (ppm)
1	5	25	<1	<1
≈ 70	≈ 100	≈ 400	6	× 230
≈ 130	≈ 400	≈ 1000	25	× 1000
1	10	20	<1	<1
≈ 30	≈ 100	≈ 400	2	× 180
≈ 96	≈ 400	≈ 1000	11	× 1000

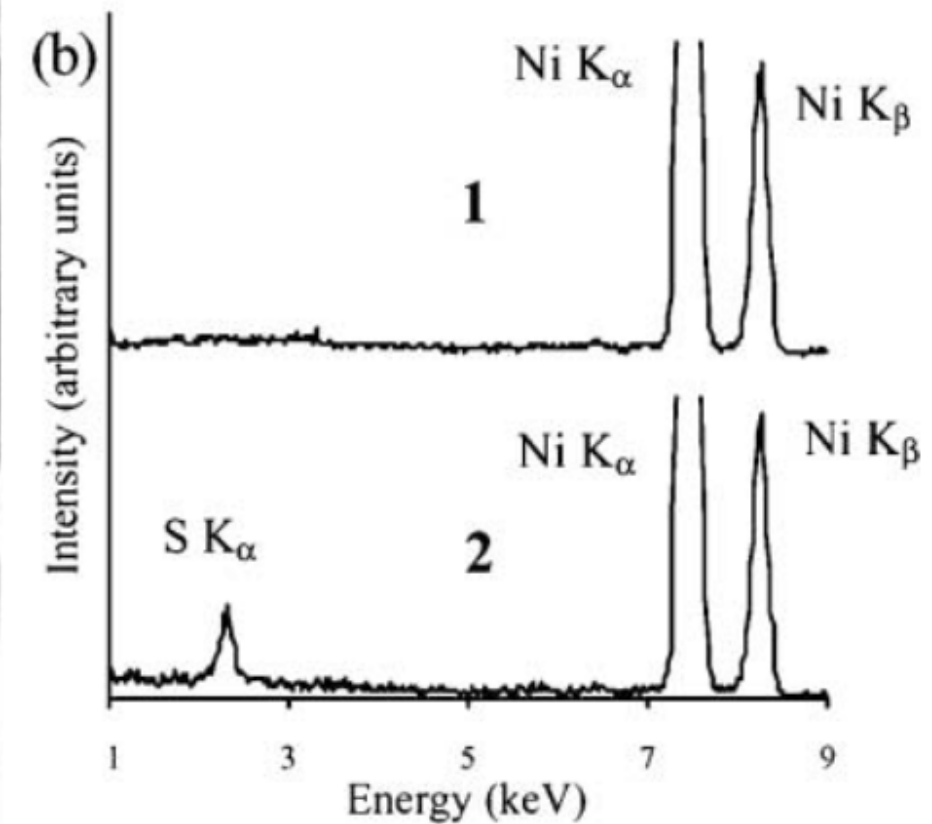
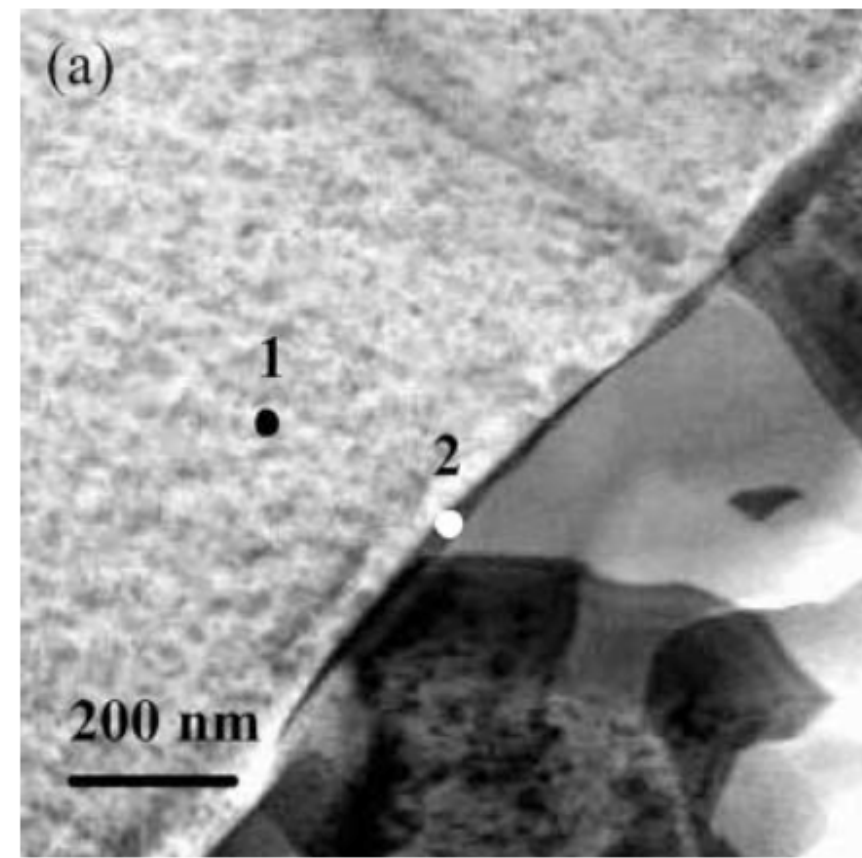
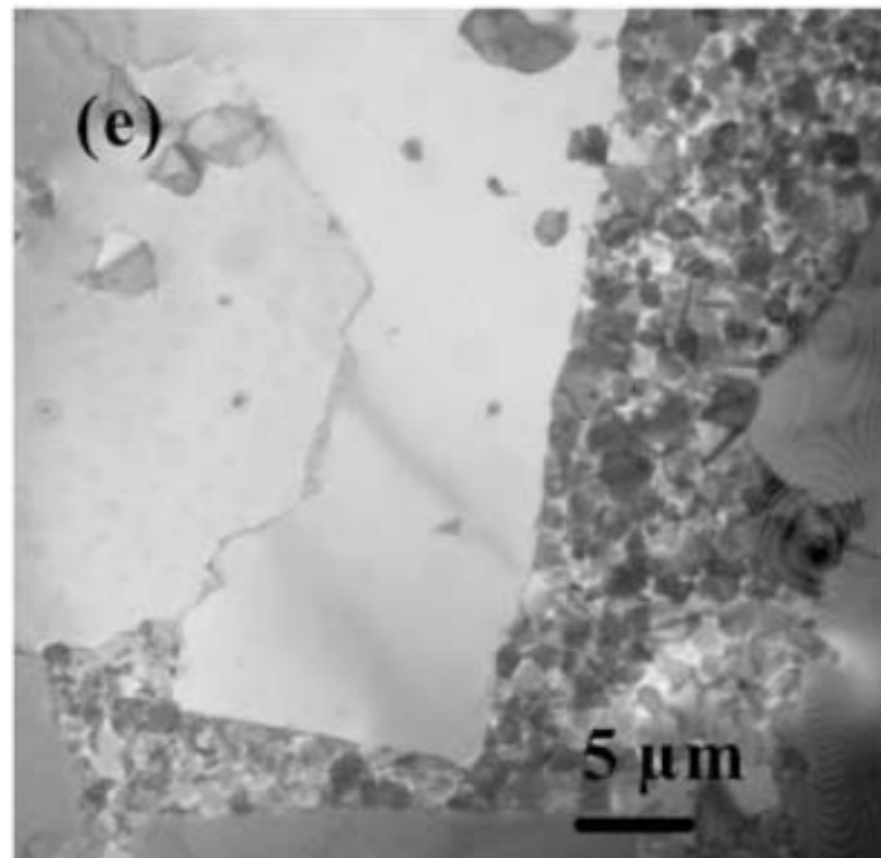
Natter H, Hempelmann R. Electrochim. Acta 2003; 49

Modified from Savall C, Godon A., Creus J, Feaugas X. Surf. Coatings Technol. 2012; 206

Impurity Sulfur in Ni

420°C - 11 Hr

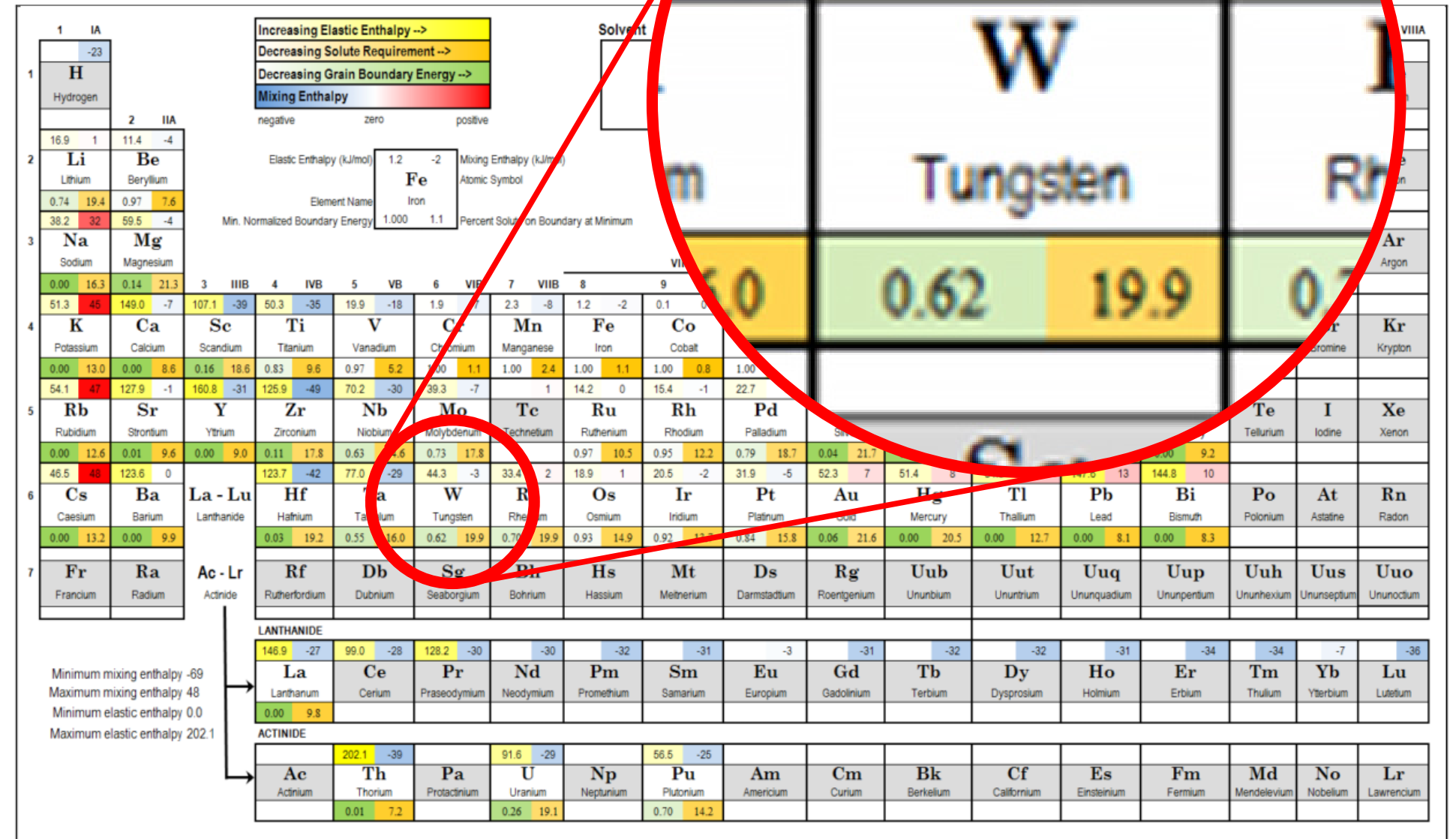
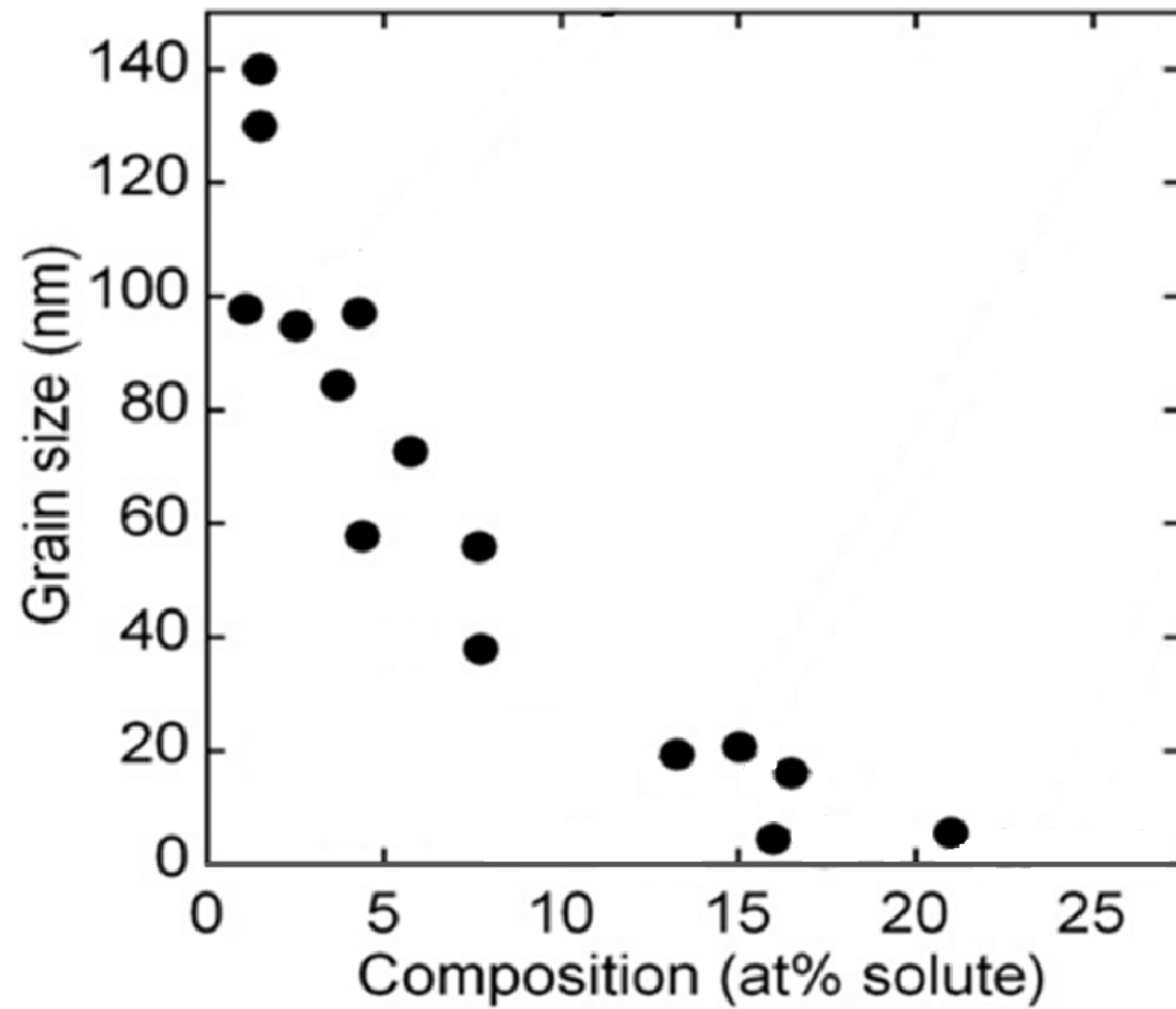
Grain Boundary EDS



G.D. Hibbard, J.L. McCrea, G. Palumbo, K.T. Aust, U. Erb, Scr. Mater. 47 (2002) 83–87.

How often does segregation *increase* grain growth rate?

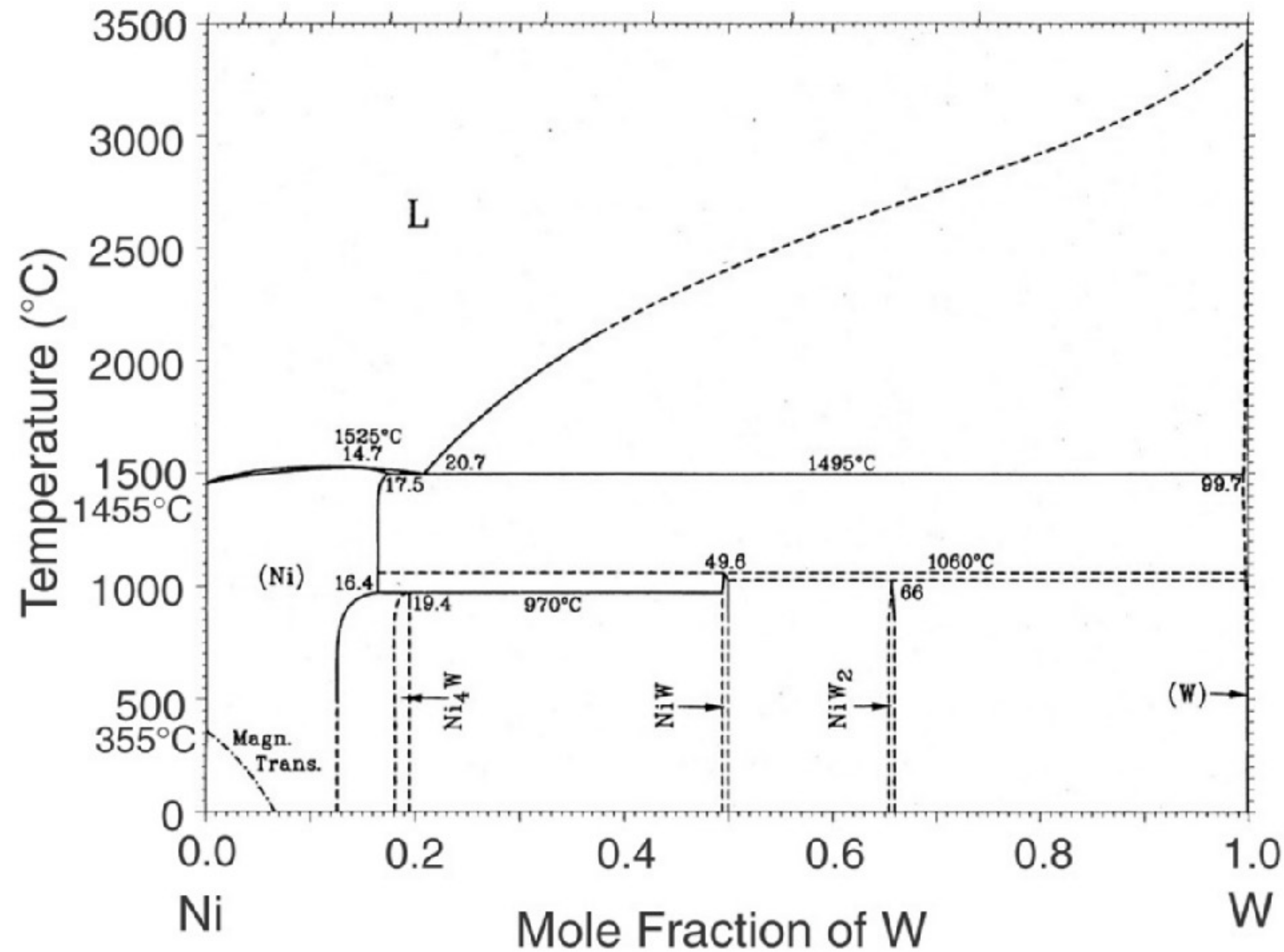
Ni-W Background



Detor AJ, Schuh CA. Acta Mater 2007;55:371.

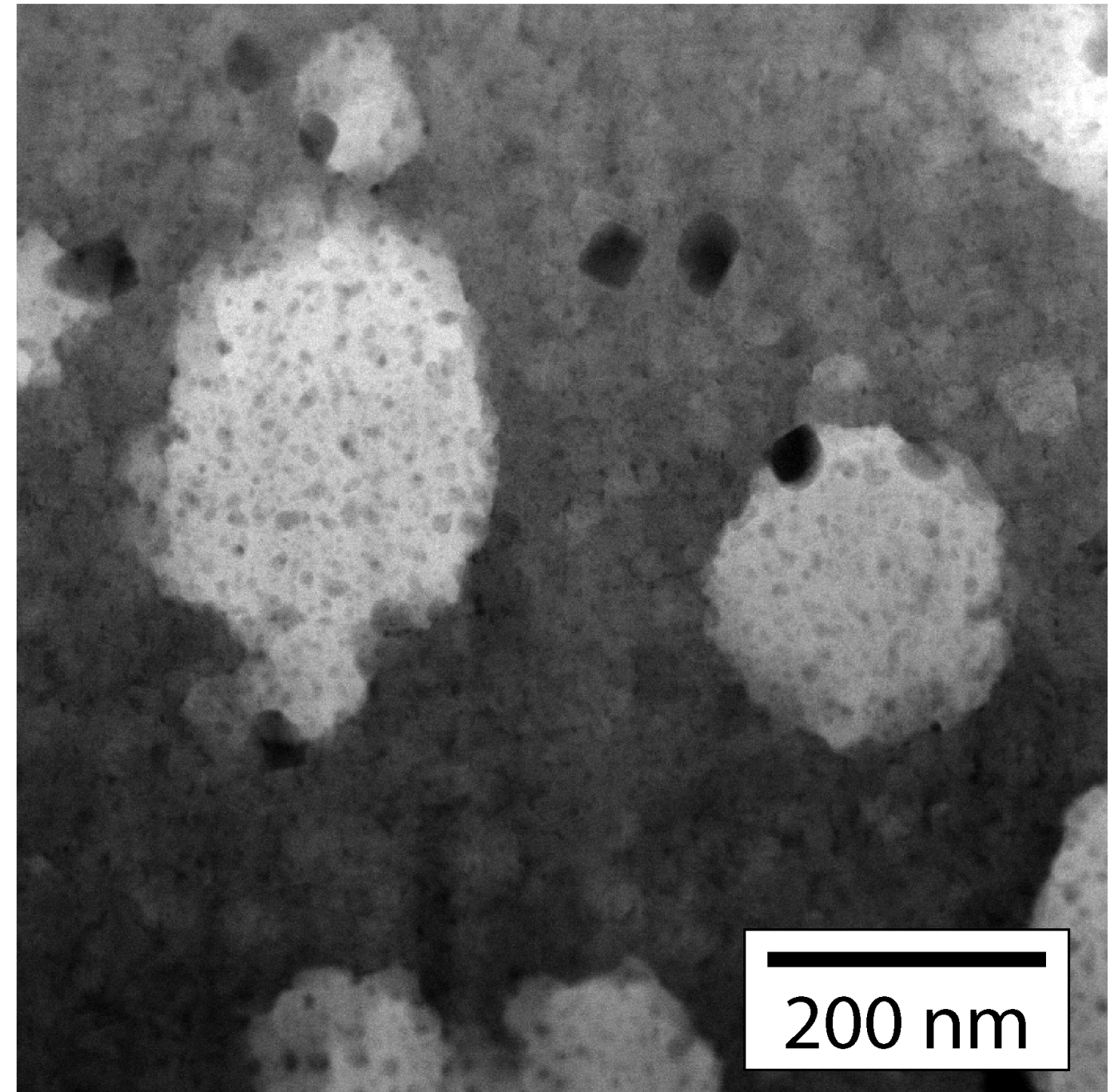
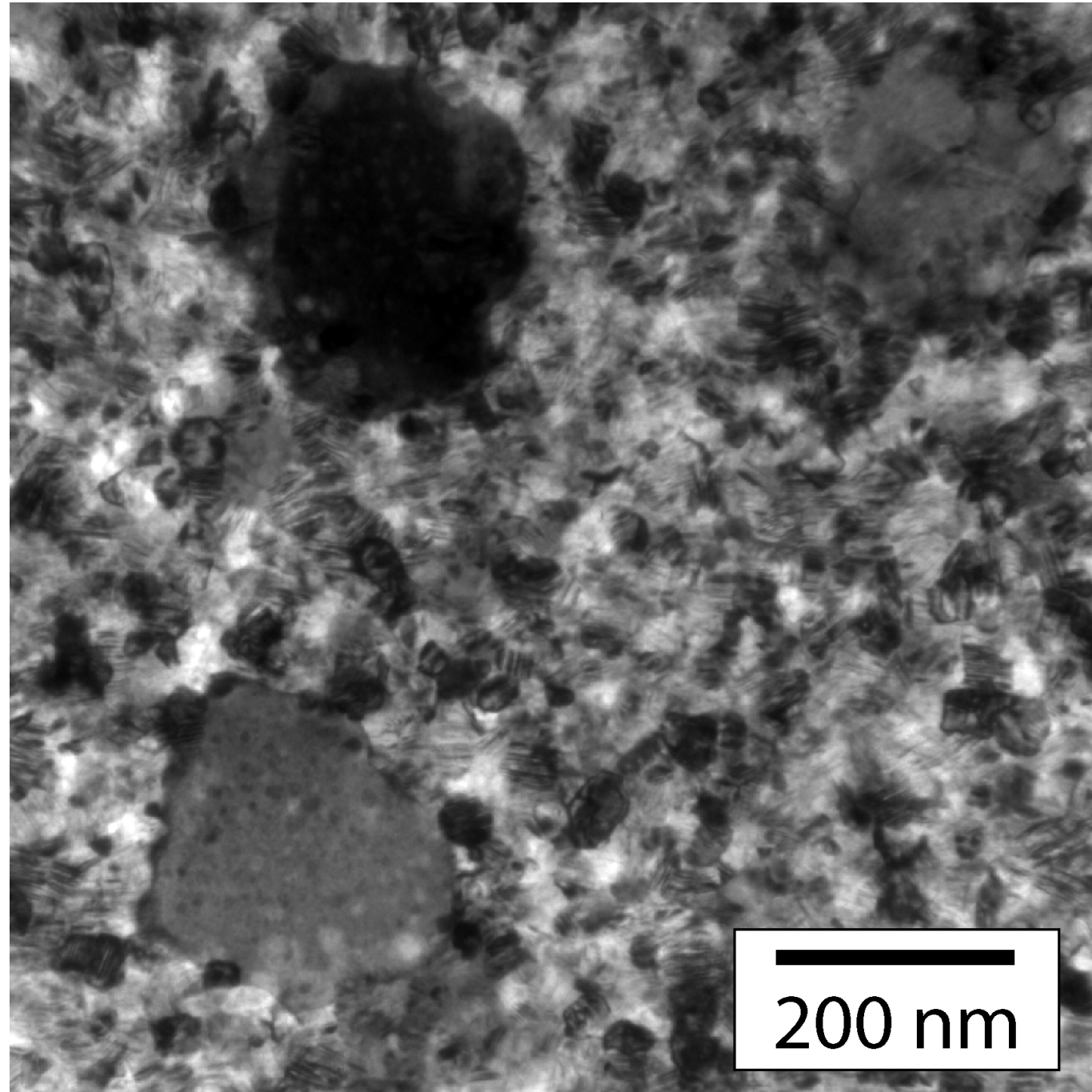
M.A. Atwater, K.A. Darling. ARL Tech Report ARL-TR-6007 2012.

Ni-W Phase Diagram



Turchi PEA, Kaufman L, Liu ZK. Calphad Comput Coupling Phase Diagrams Thermochem 2006;30:70.

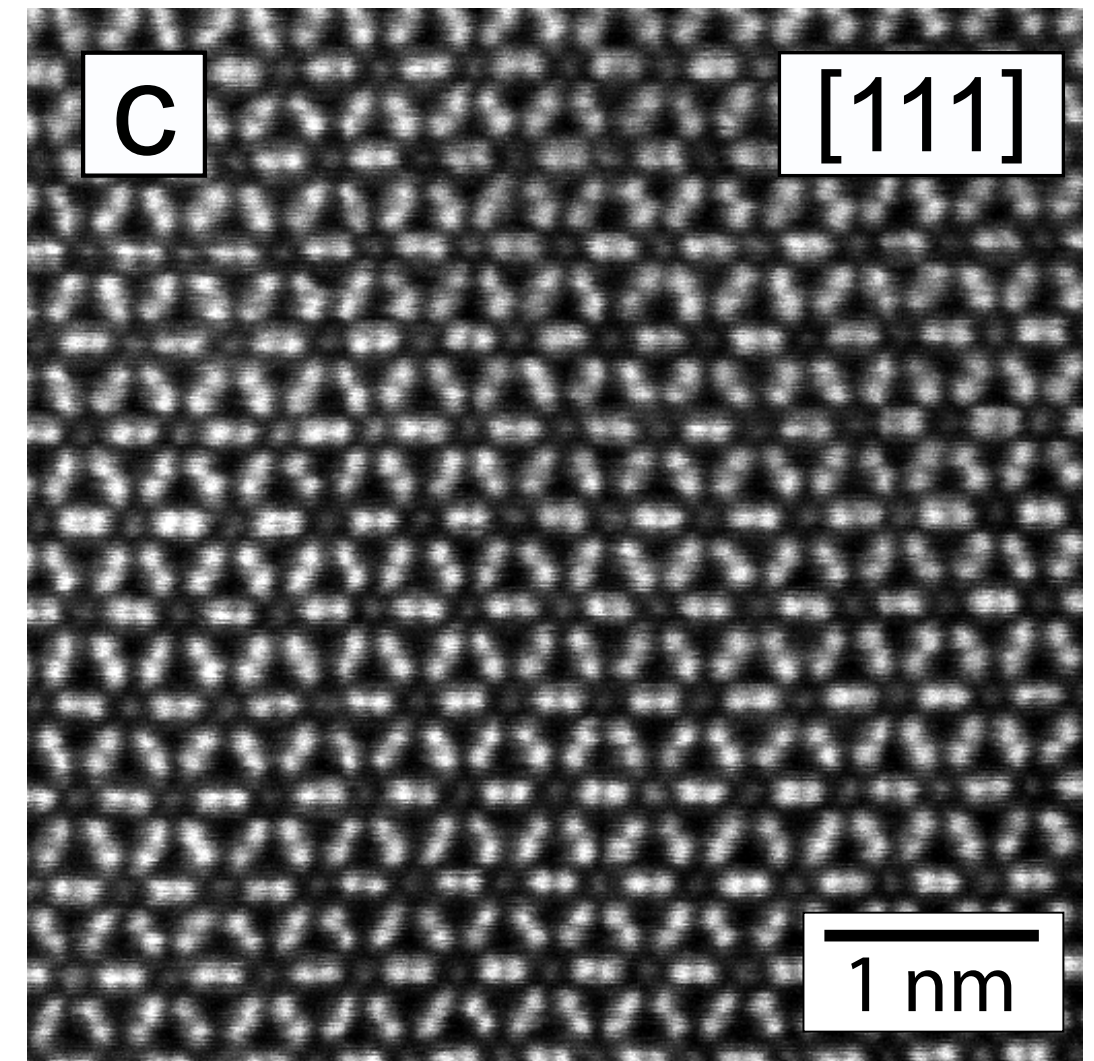
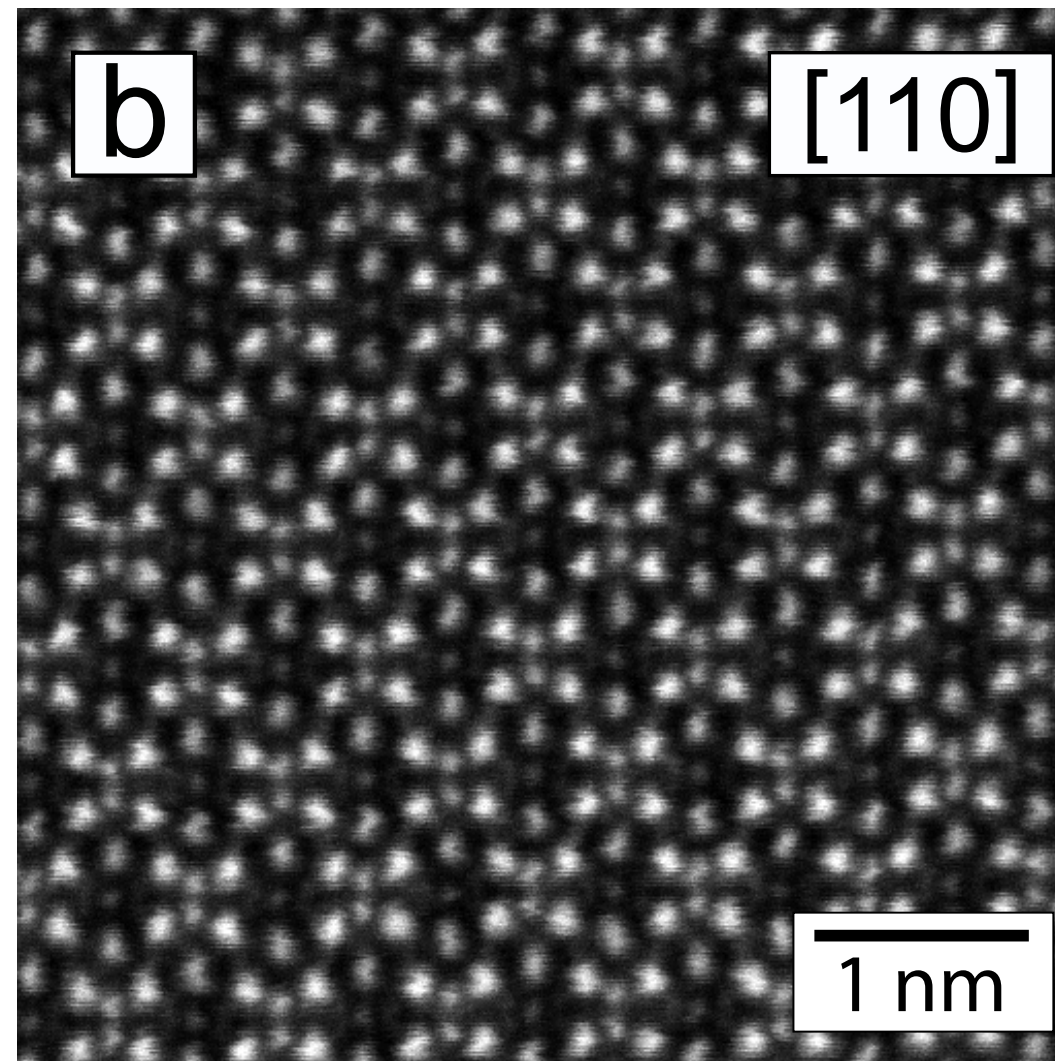
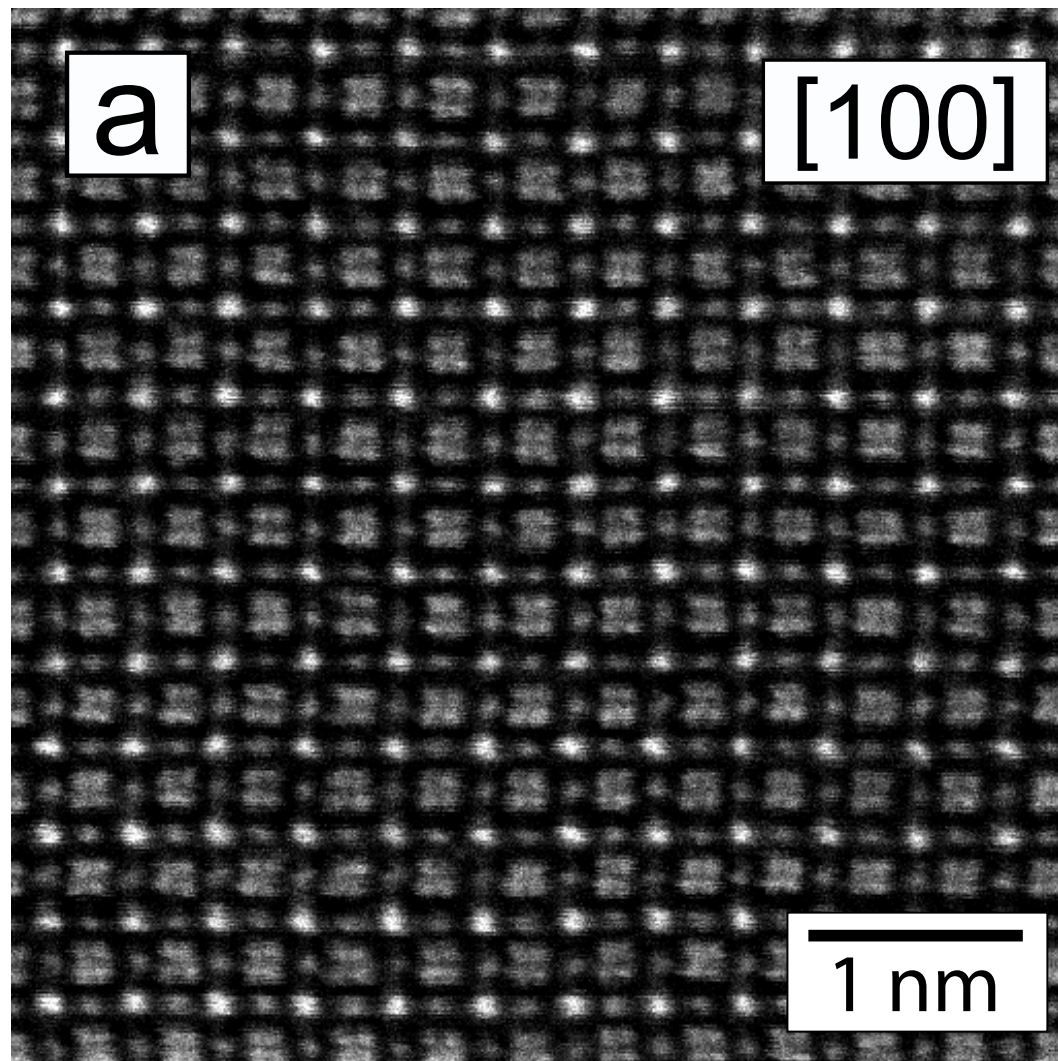
Electroplated Ni-W: Initial Analysis



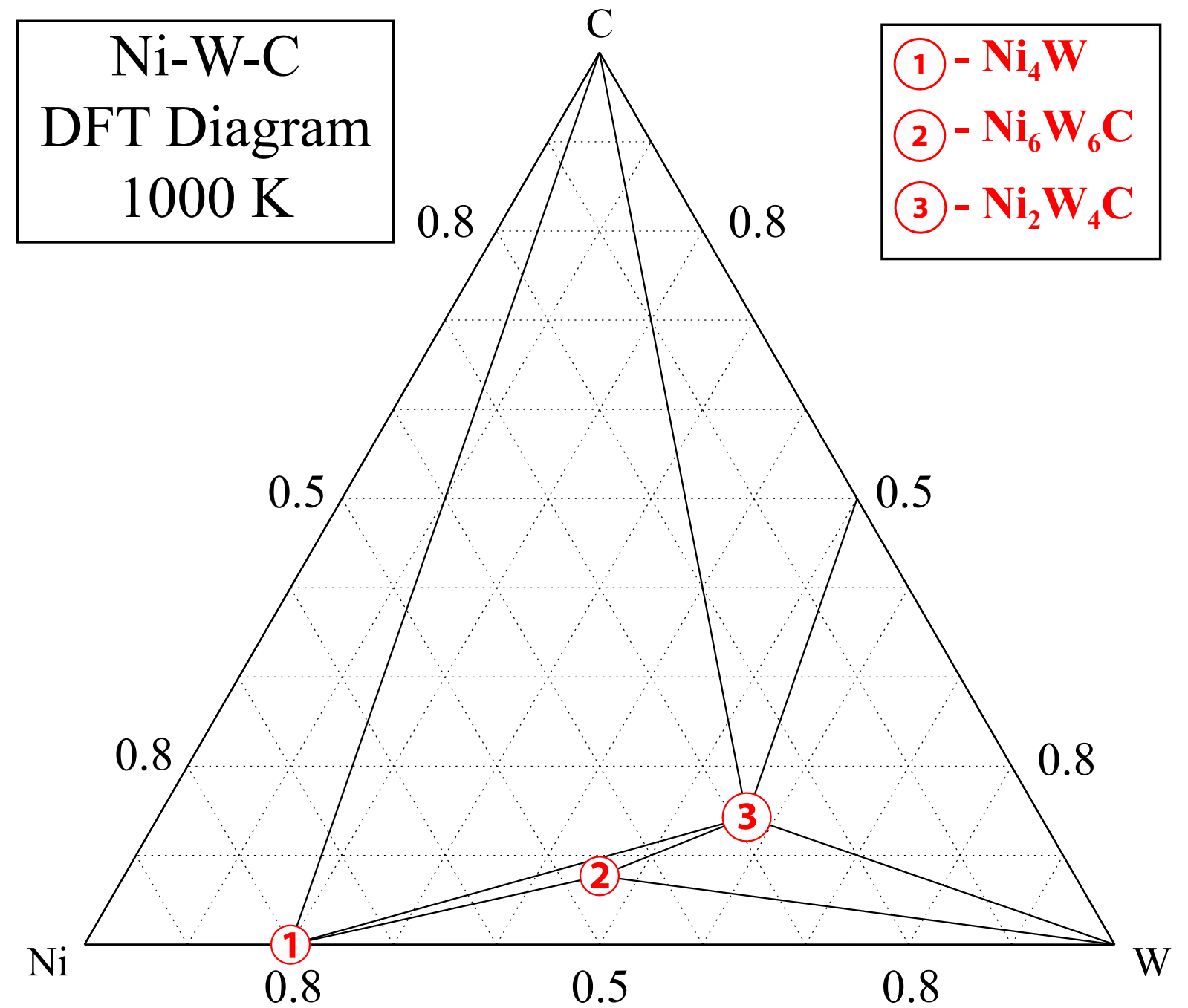
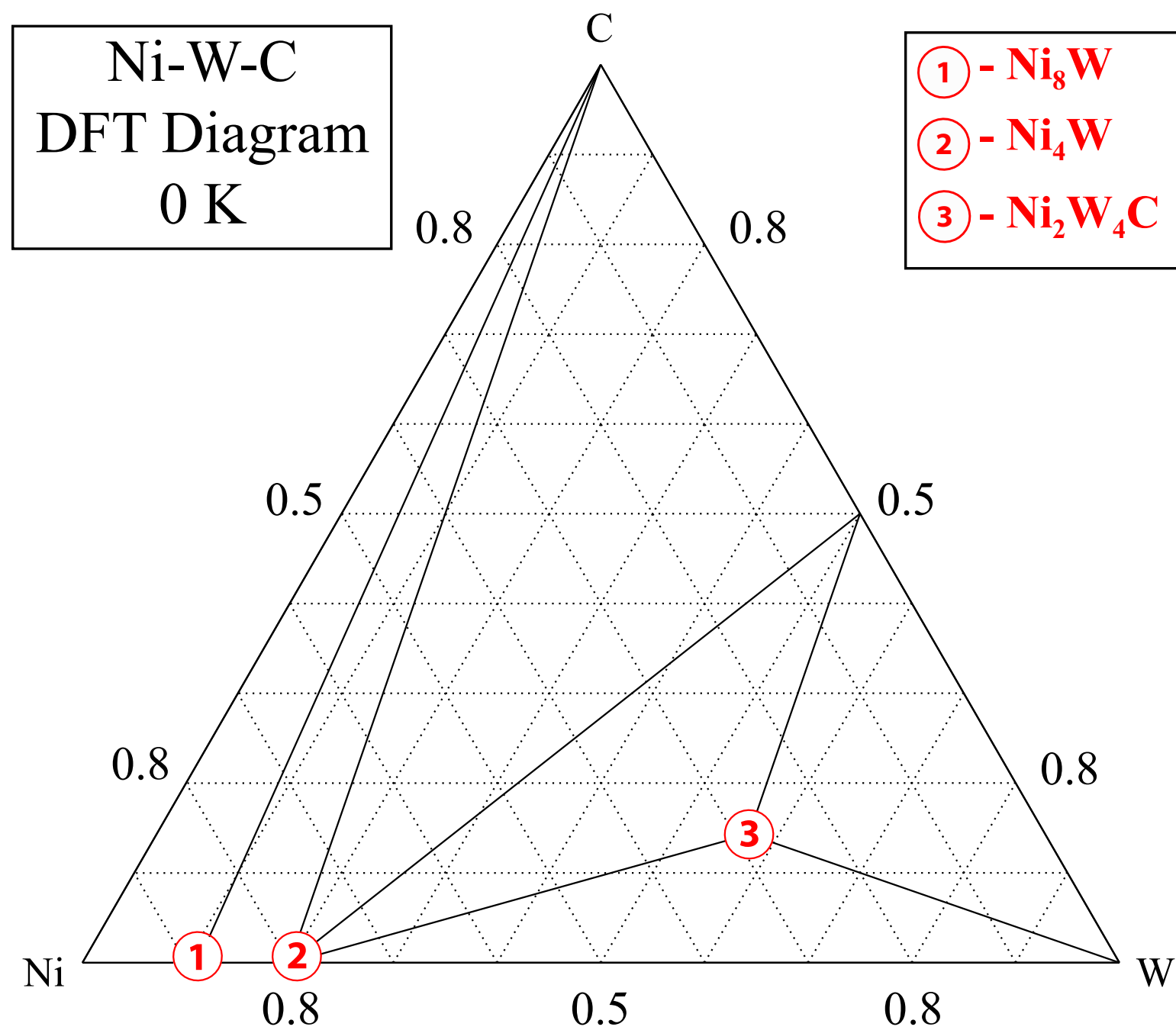
Several unknown phases → Do not match phase diagram

Bright phase is $\text{Ni}_6\text{W}_6\text{C}$

$\text{Ni}_6\text{W}_6\text{C}$ is misidentified as intermetallic NiW

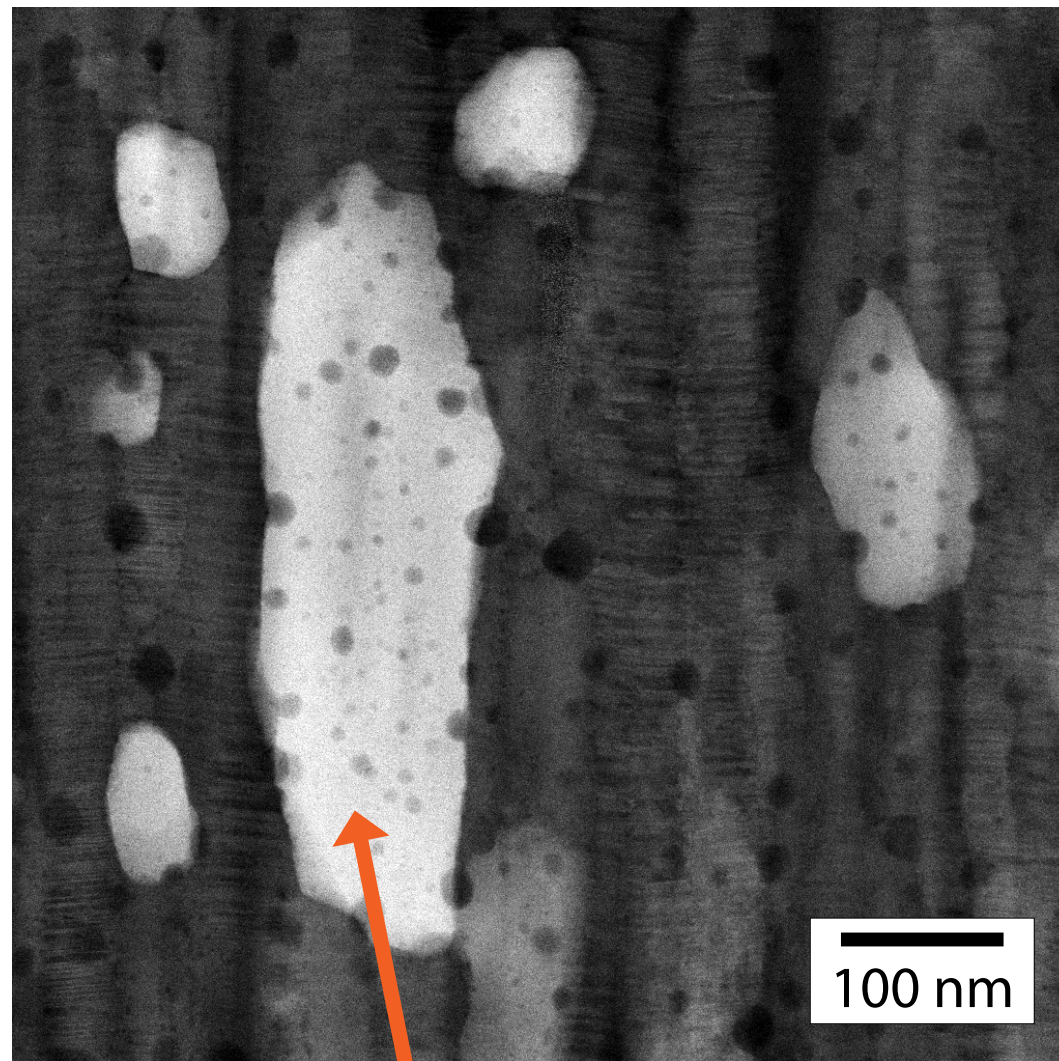


Ternary DFT phase diagrams

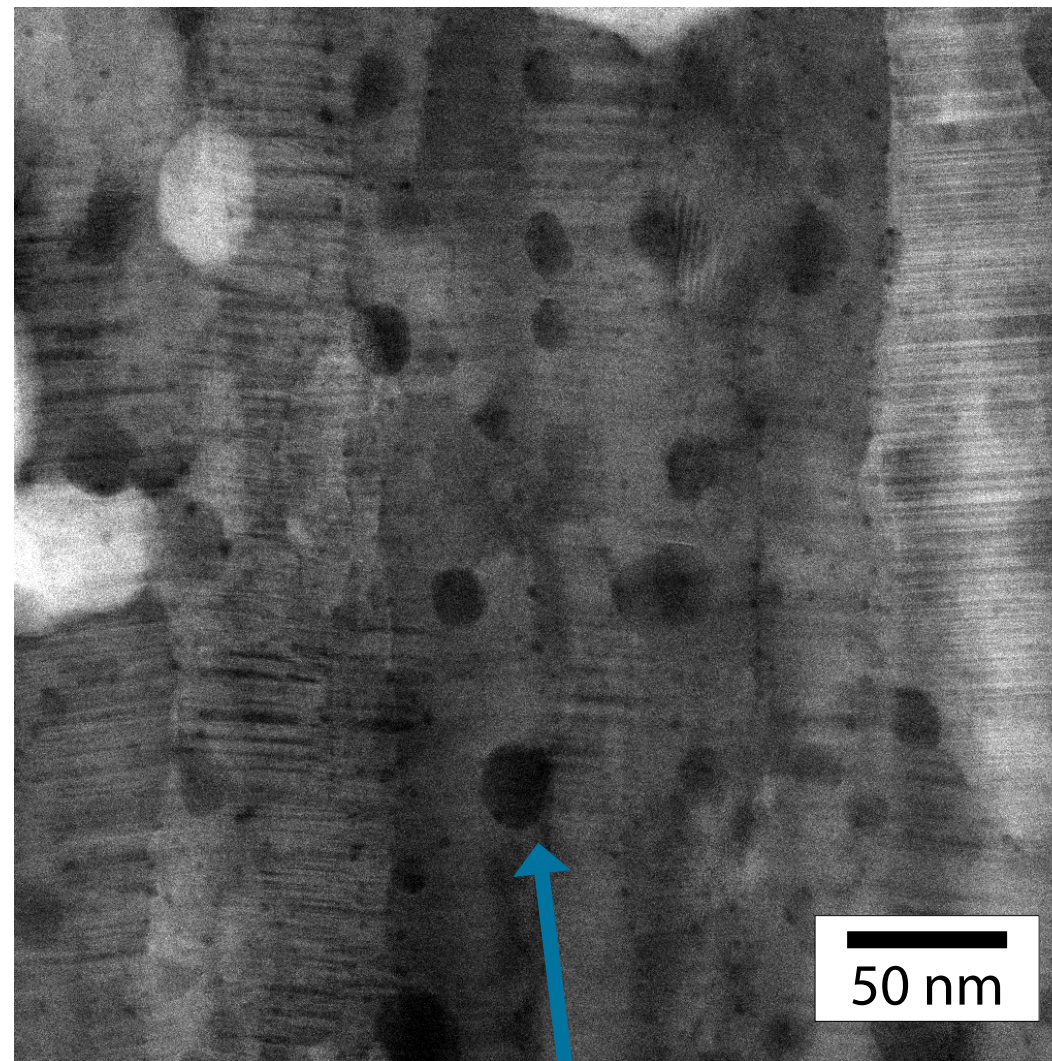


Ni₆W₆C (and others) in sputtered films

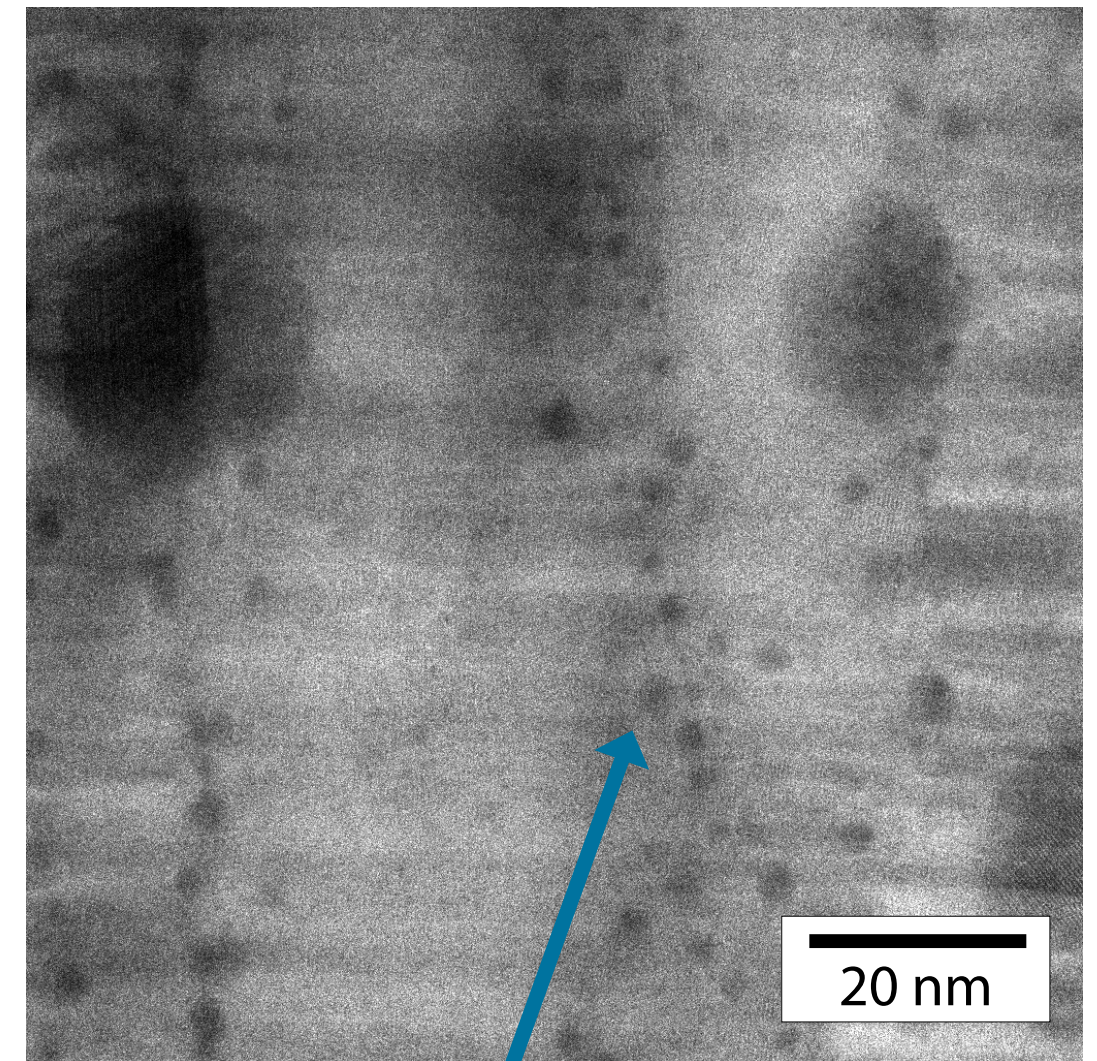
Impurity phases may be more common than realized



Carbide

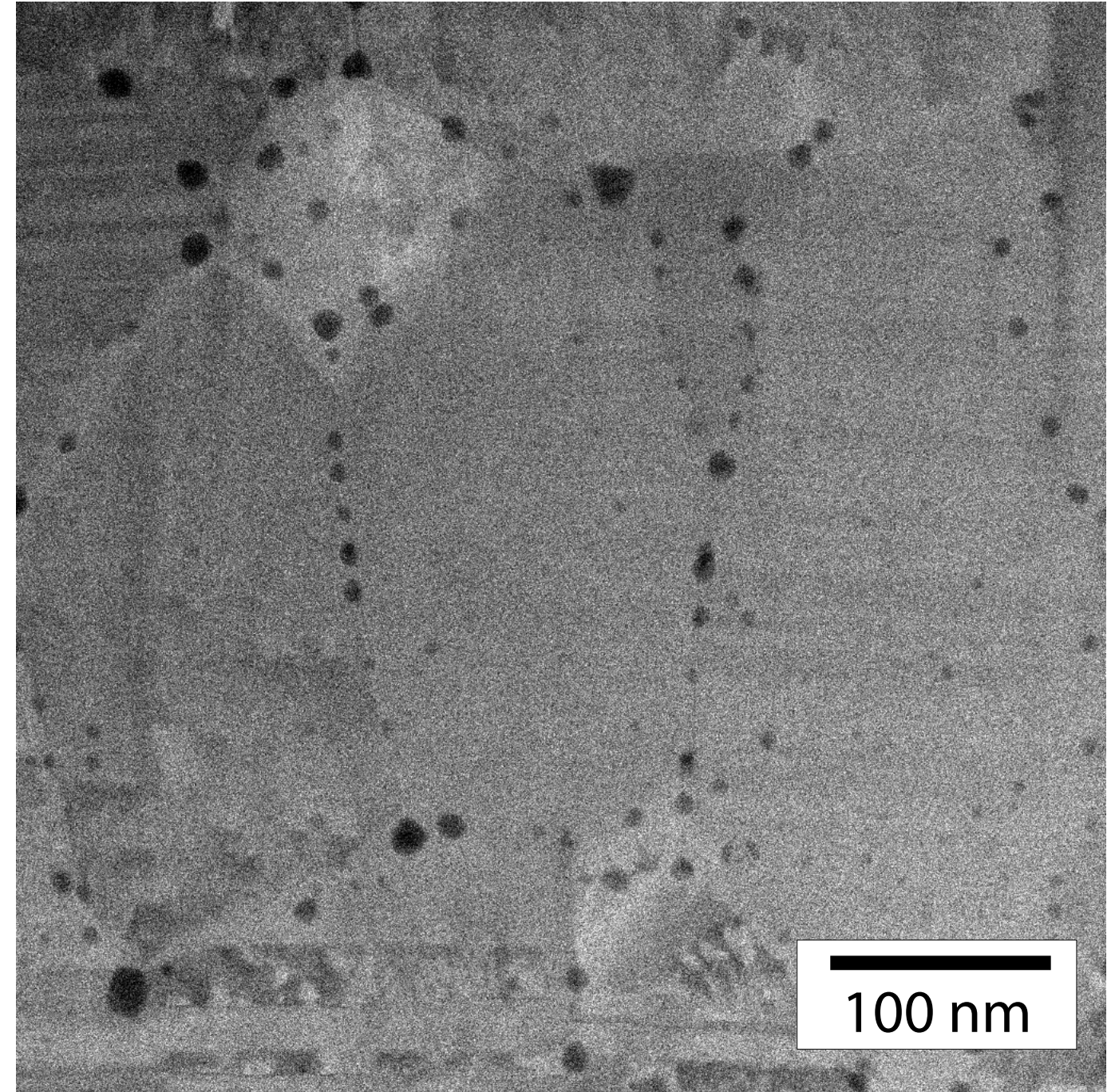
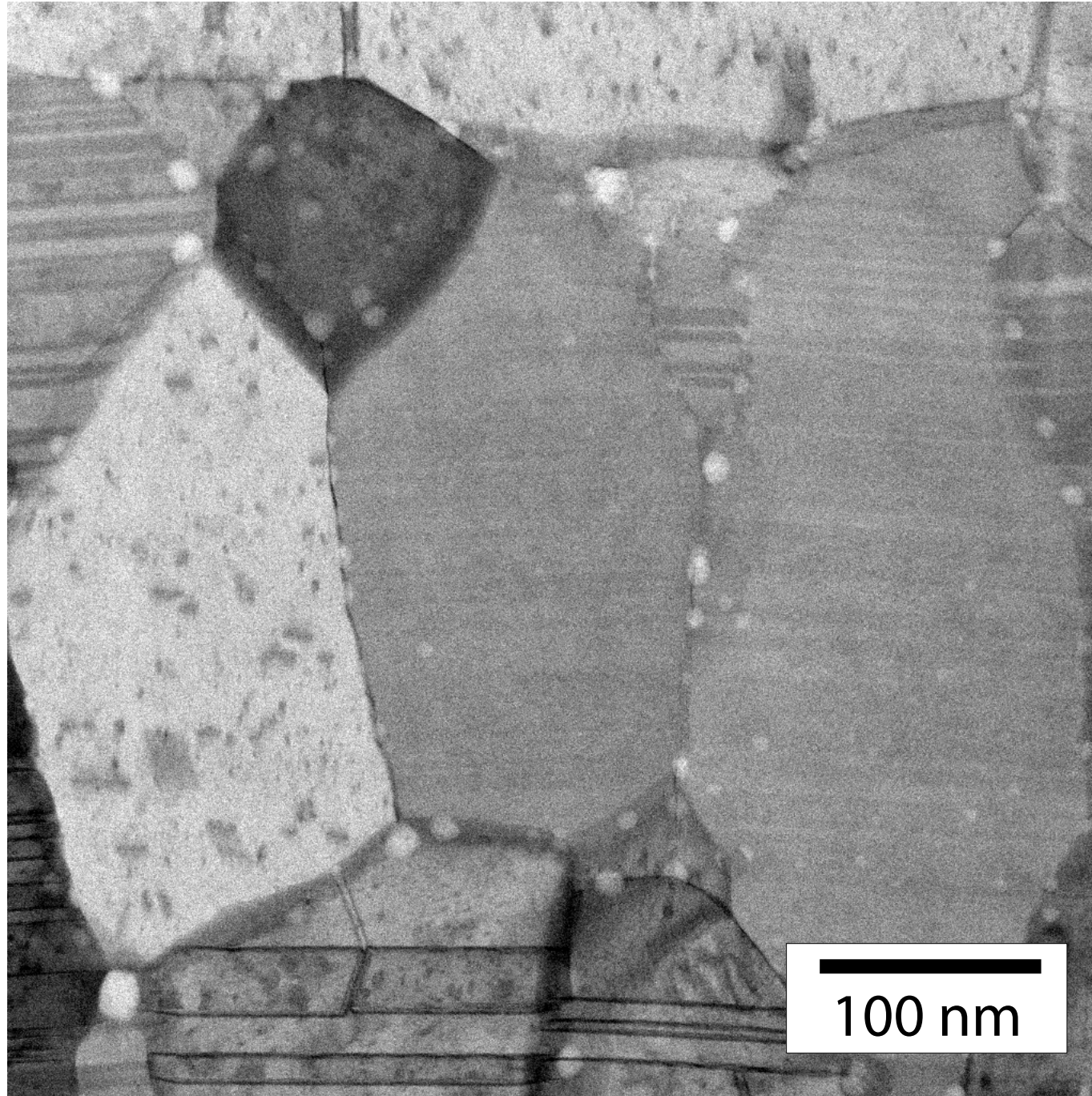


**Oxides &
Large Ar Pores**

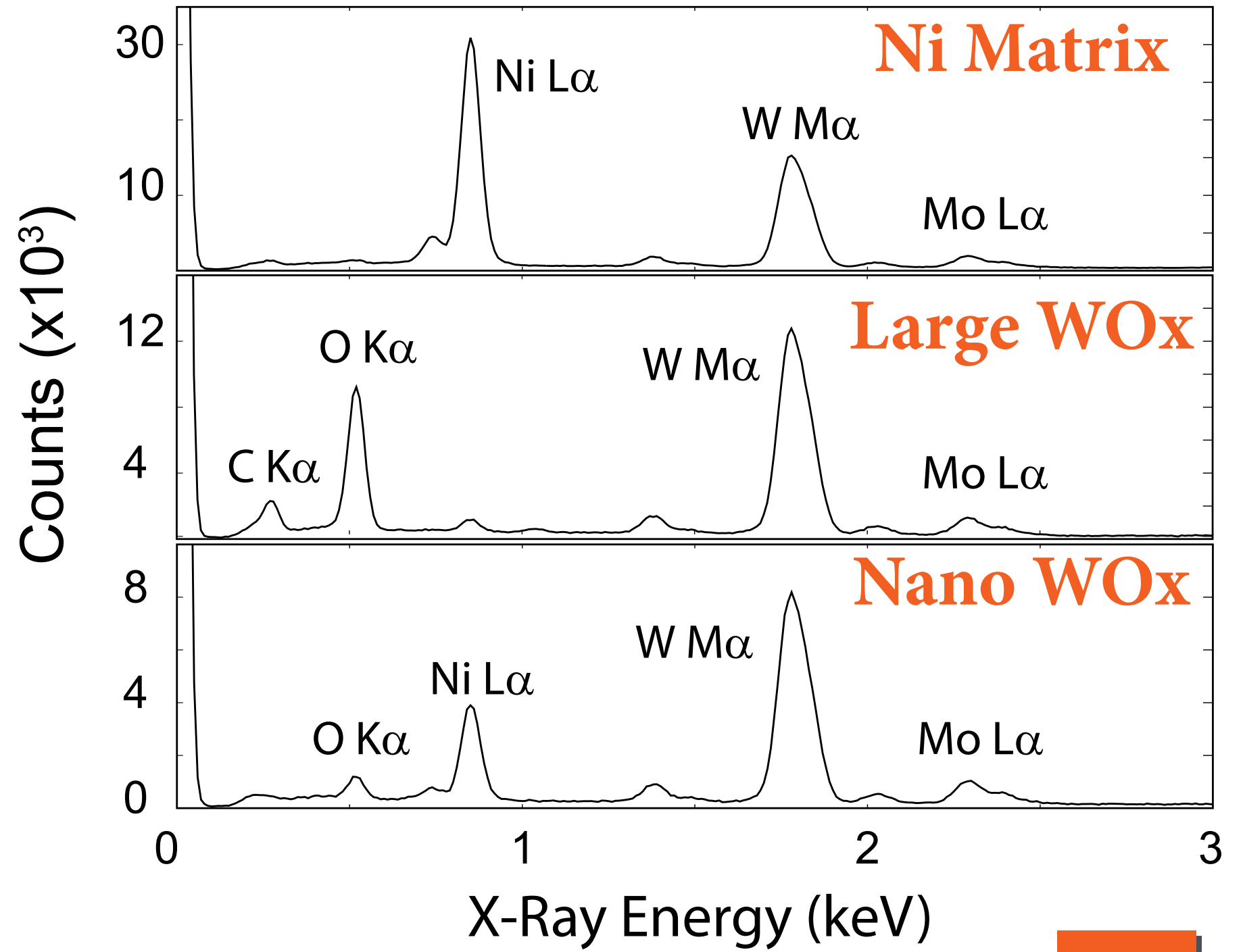
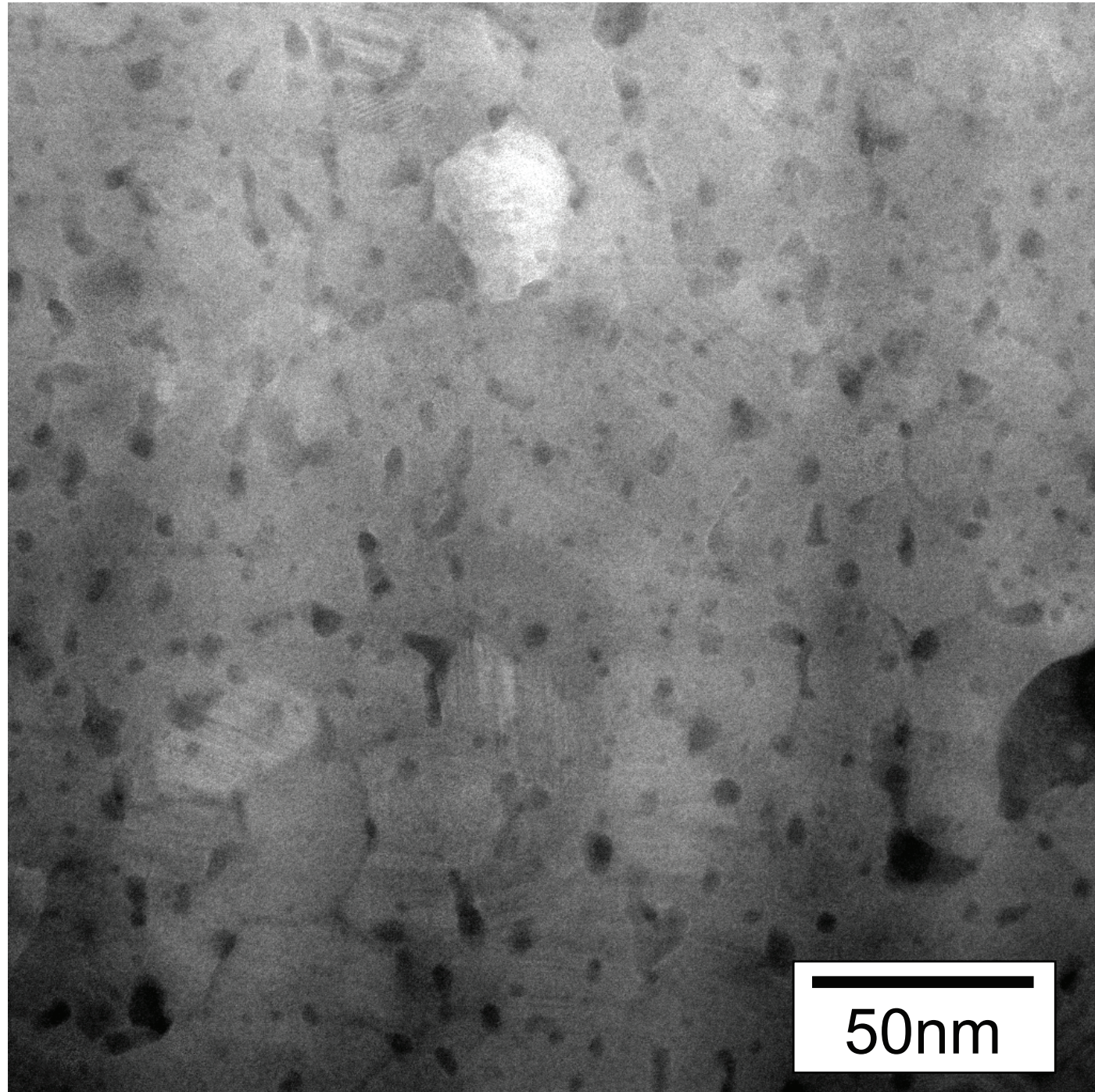


Small Ar Pores

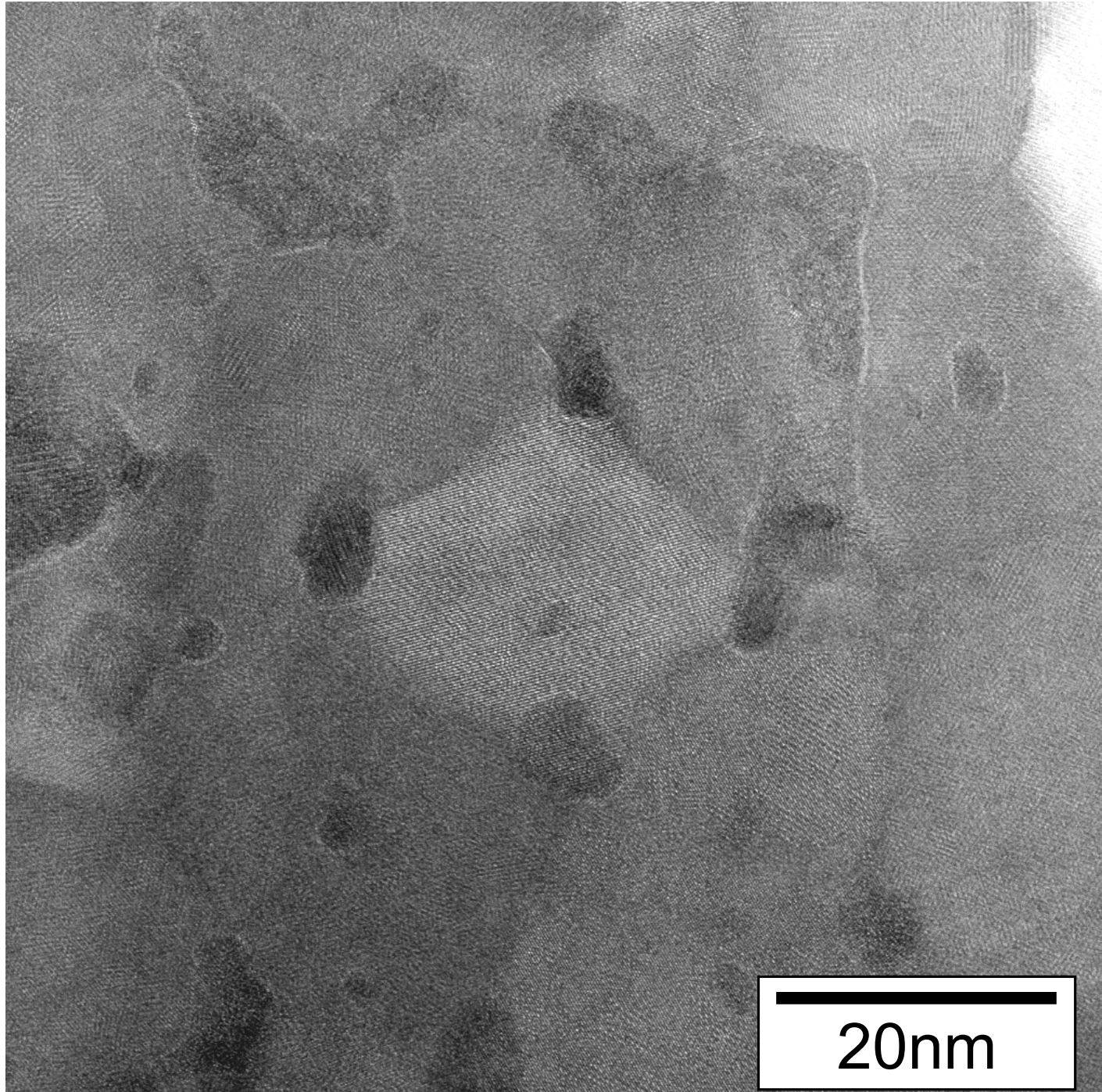
Ar pores pin grain growth?



Dark phase is W-rich oxide



Nanoscale oxides pin grain growth?



Grain Radius ≈ 30 nm

Particle Radius ≈ 3 nm

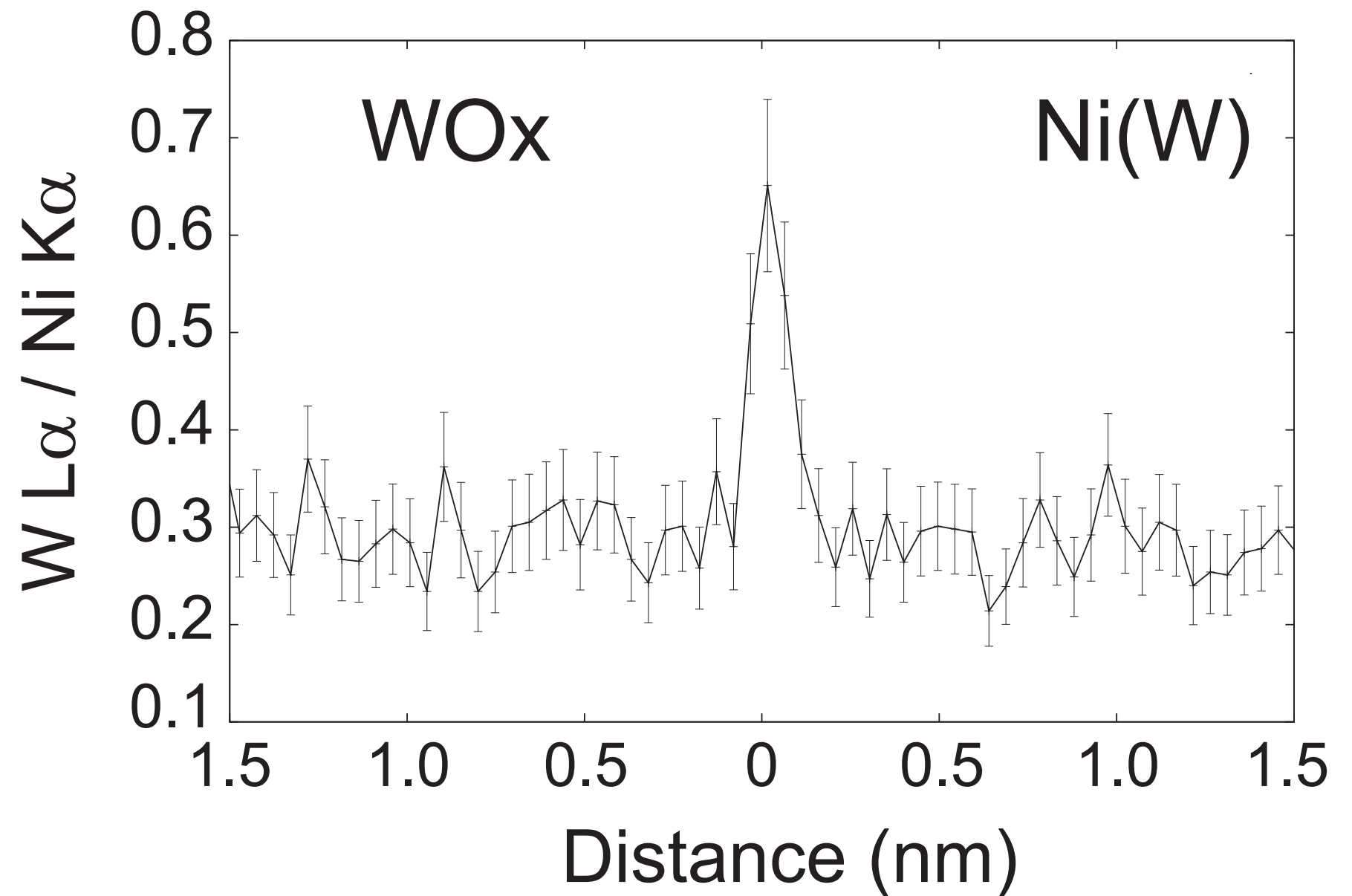
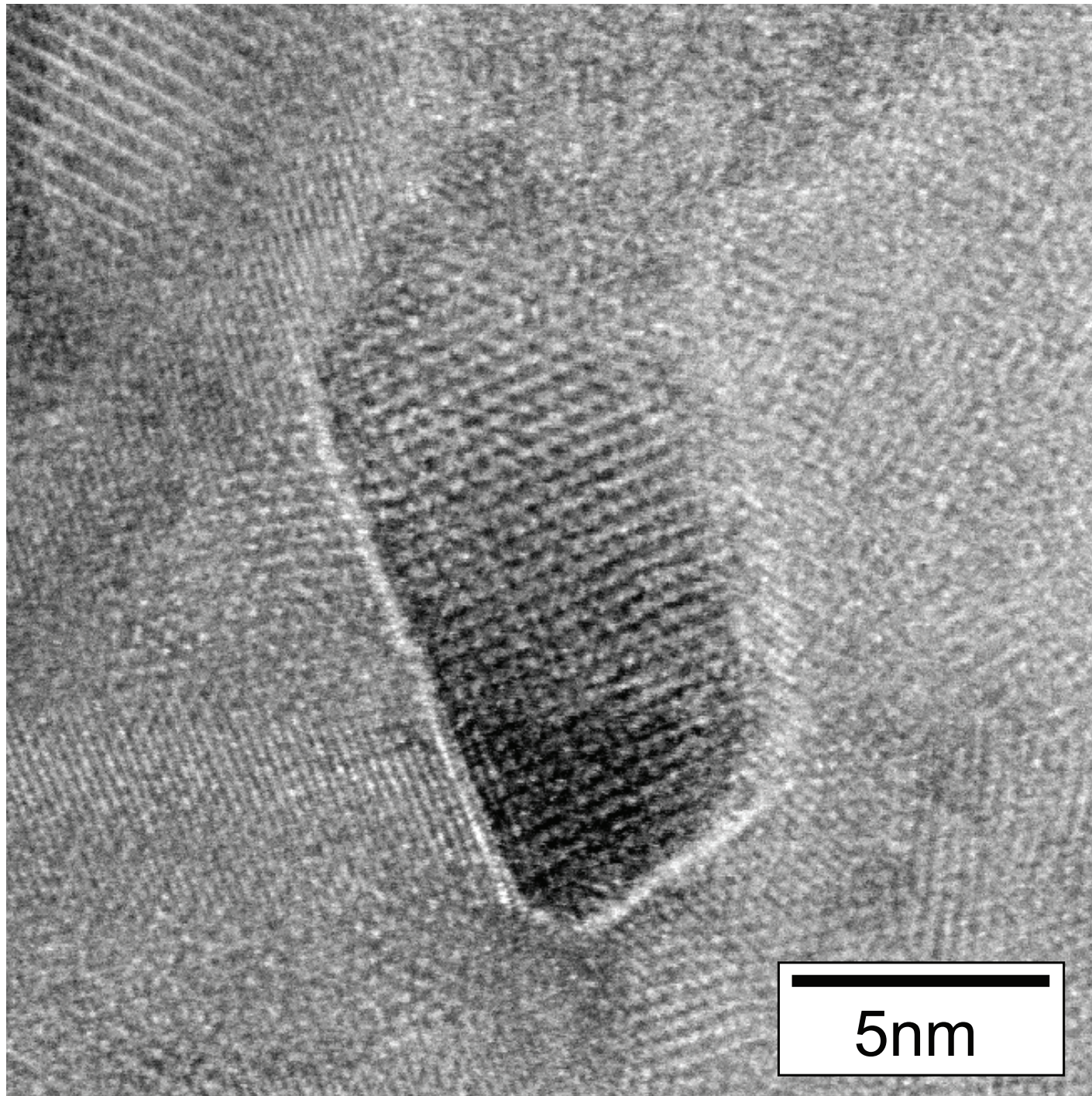
Measured Volume Fraction $\approx 3\%$

What volume fraction do we need?

$$f_{\text{critical}} = \frac{r}{5R} = \frac{3\text{nm}}{150\text{nm}} = 2\%$$

R.D. Doherty, Mater. Sci. Forum 715-716 (2012) 1-12.

WO_x Segregation

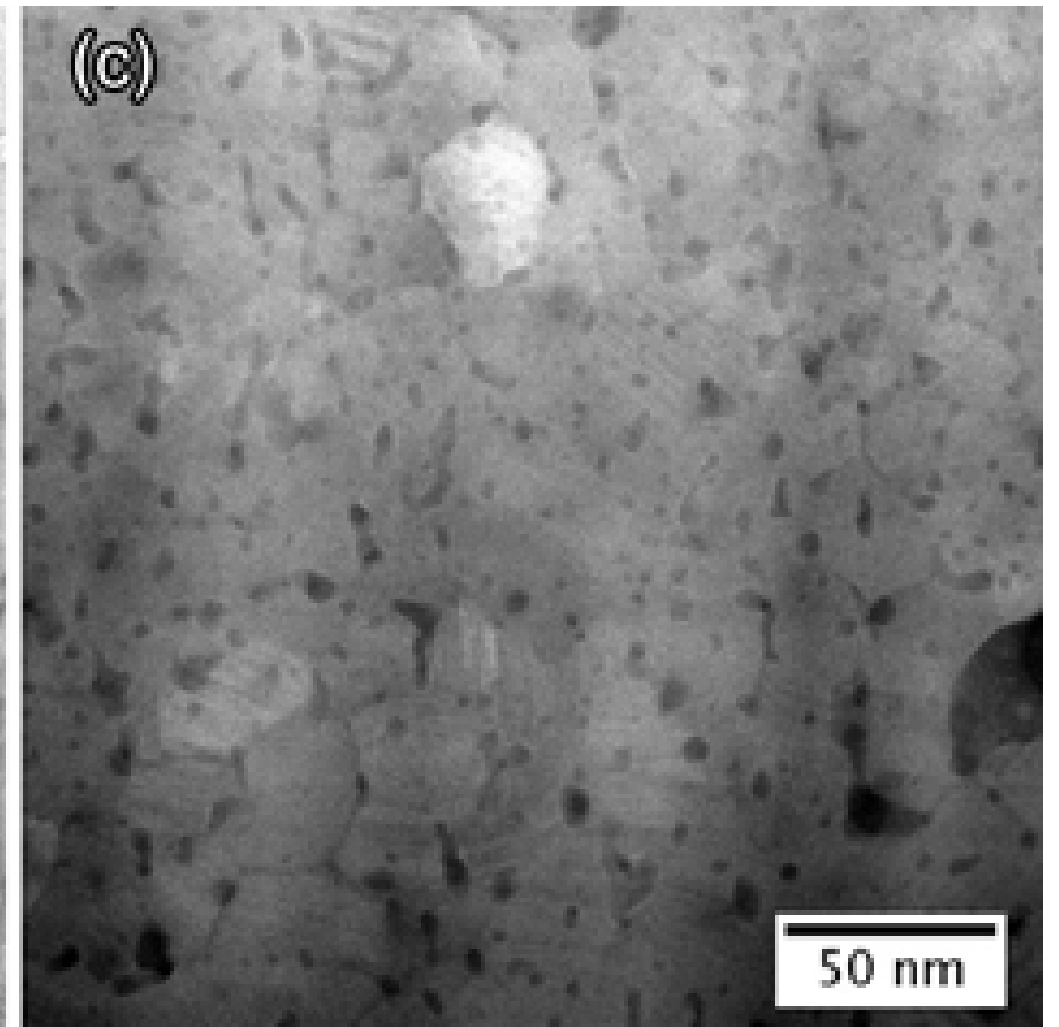
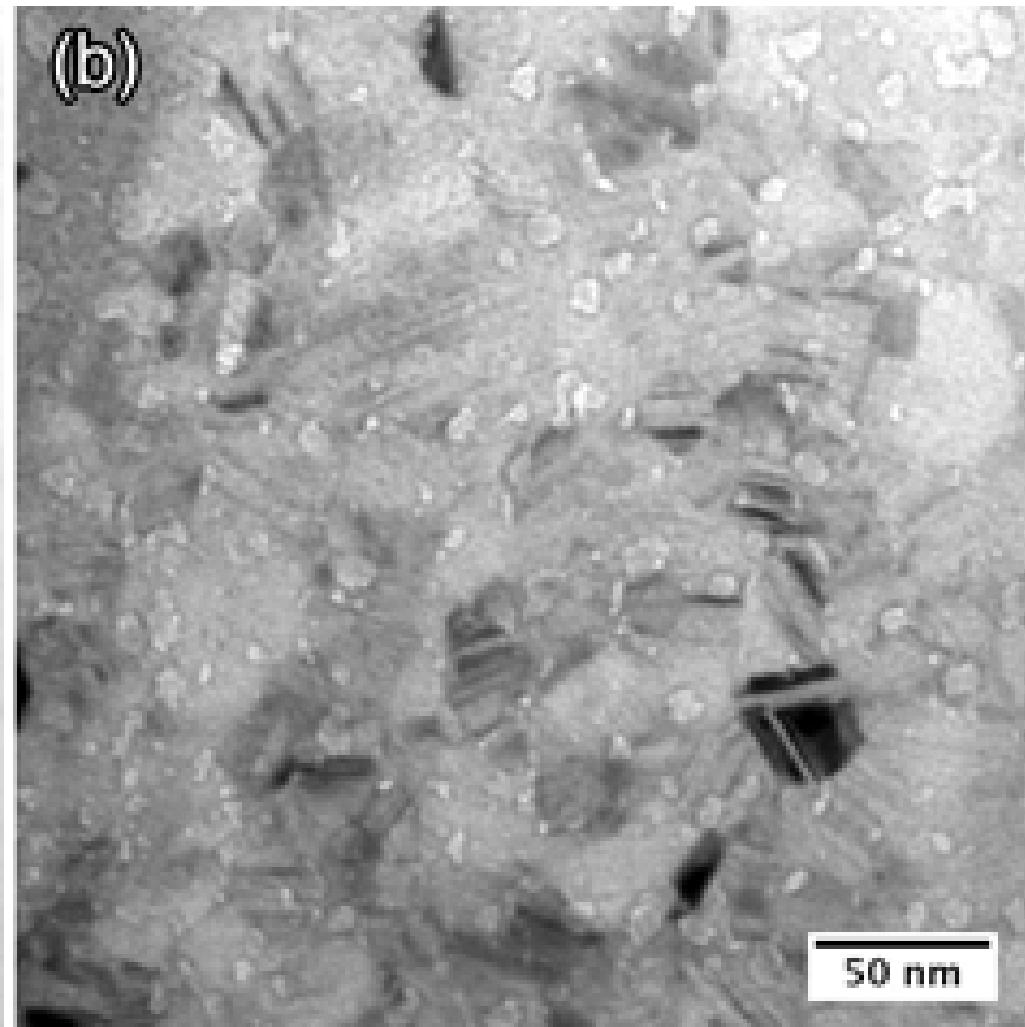
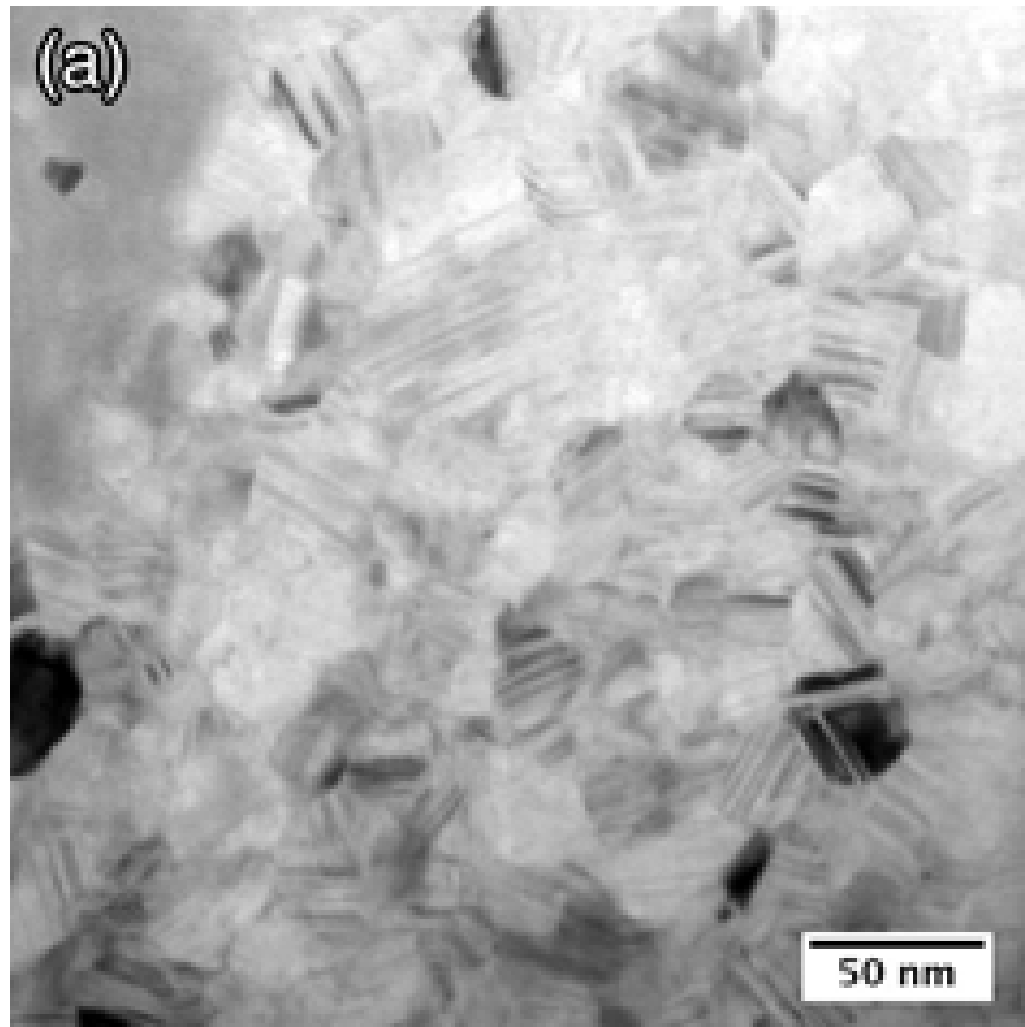


Finding the oxides

Focused TEM-BF

Underfocused TEM-BF

STEM-HAADF

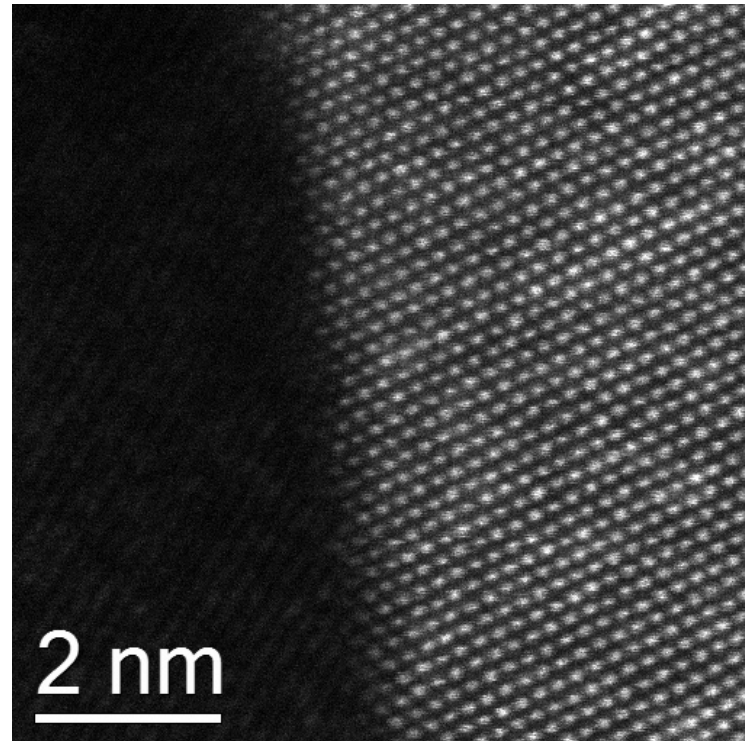


Search for W-segregation

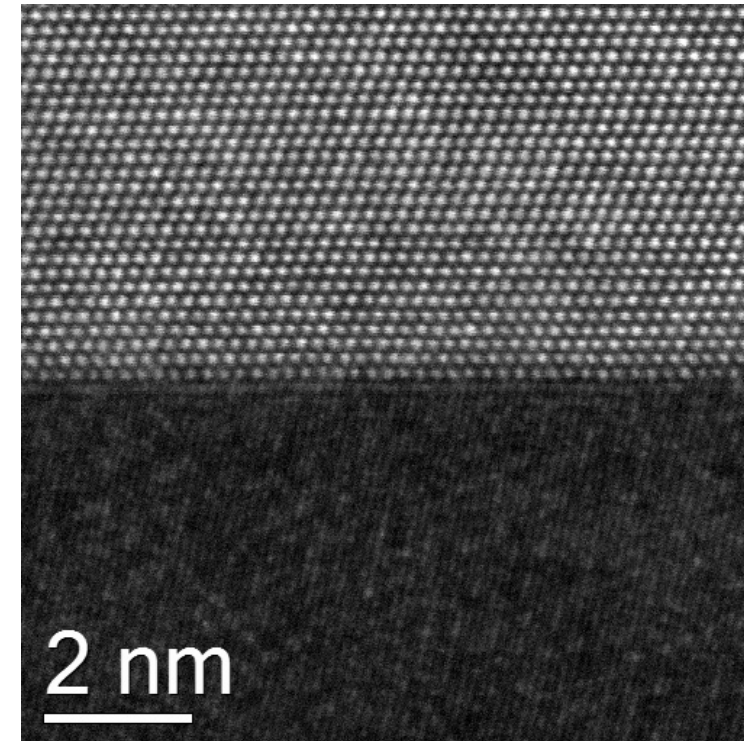
As-Deposited

700°C

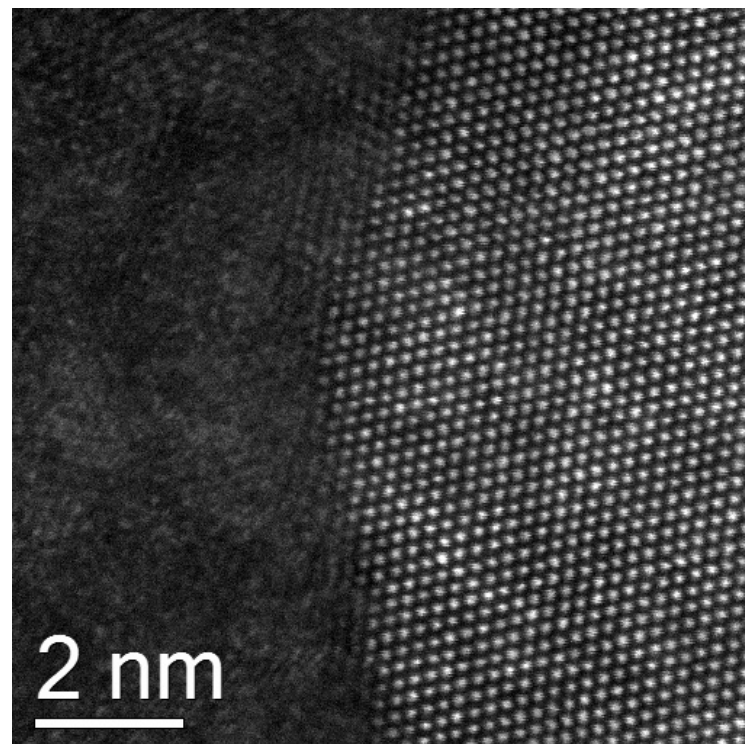
3at%



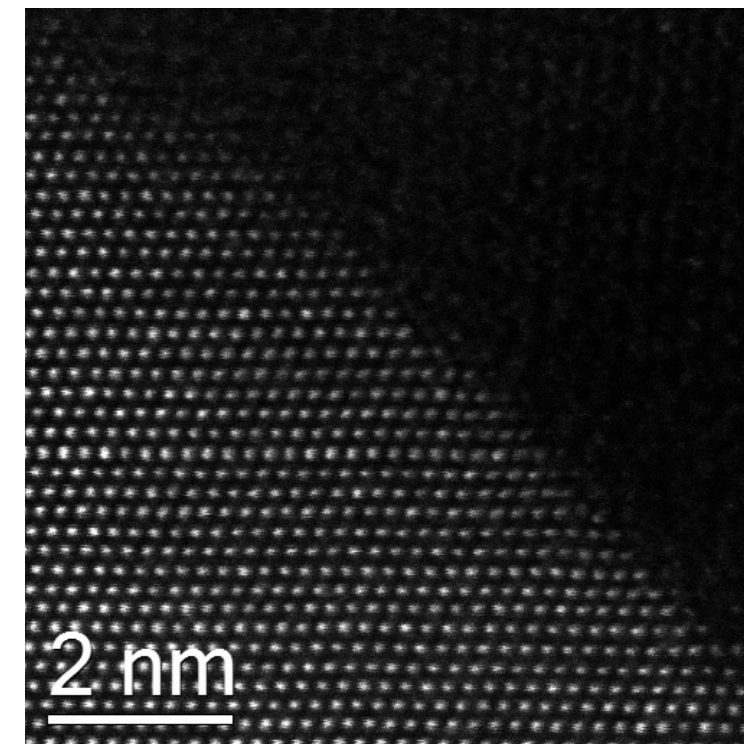
9at%



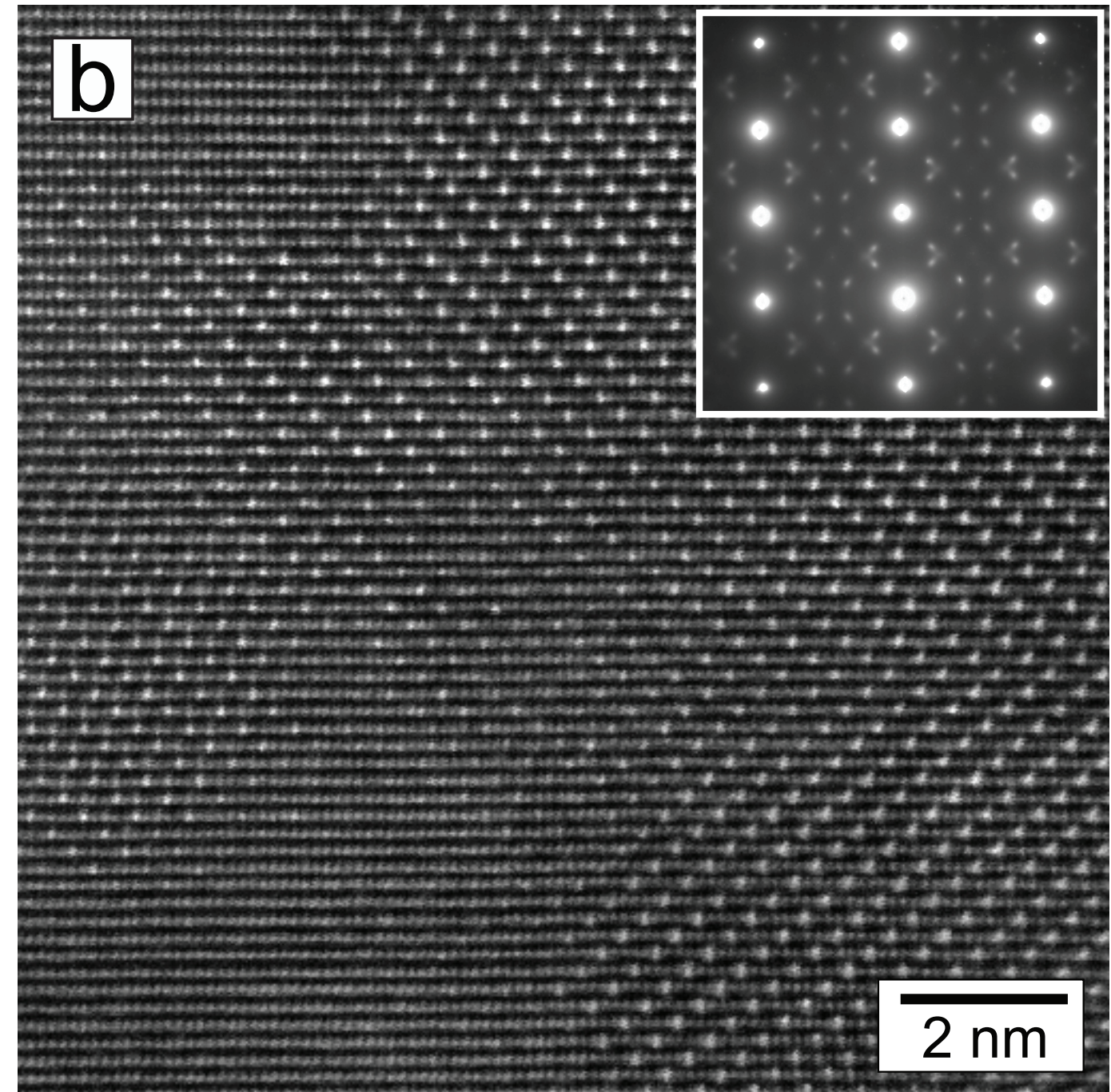
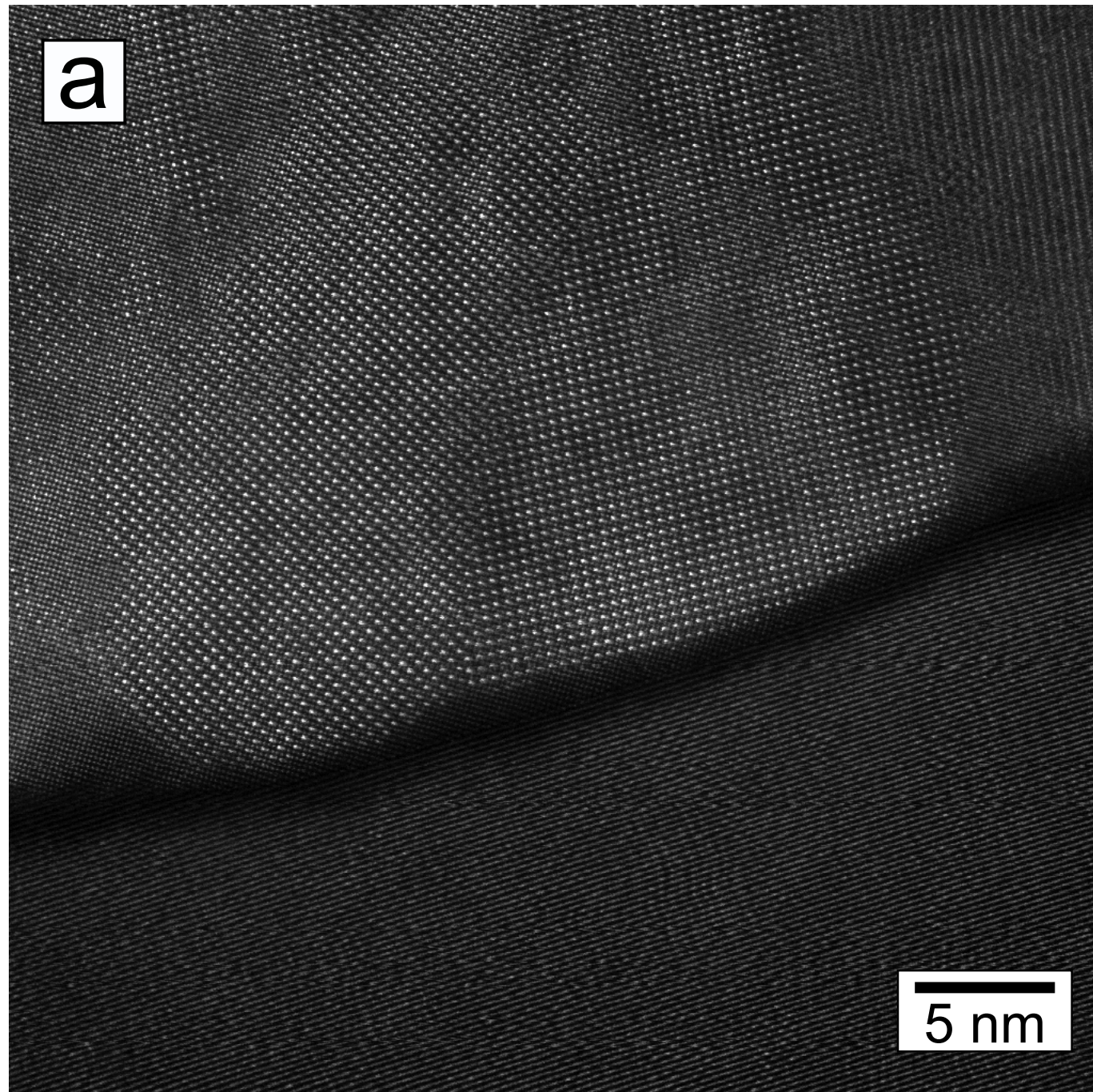
11at%



23at%



Ni_4W nucleate from W-rich boundaries?



A few open questions...

1. Is Ni-W an isolated example?
2. How pure is pure and do we care?
3. Can we dope nanograin materials with “impurities”?
4. Do we trust our computational models?
5. Are all nanocrystalline grain boundaries equal?
6. Can we truly characterize nanocrystalline microstructures?